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Review



Mechanistic investigations of emerging type-II, Z-scheme and S-scheme heterojunctions for photocatalytic applications – A review

Alisha Shabbir^a, Sabahat Sardar^b, Asad Mumtaz^{a,*}

- a Department of Chemistry, School of Natural Sciences (SNS), National University of Sciences and Technology (NUST), H-12, Islamabad 44000, Pakistan
- ^b Research and Development (R&D) Division, Al Qasim Traders, H-13, Islamabad 44000, Pakistan

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ABSTRACT

Photocatalysis is considered to be the most promising route for remediation of the environment by degradation of pollutants and production of environment friendly fuels. There are two major factors that affect the efficiency of photocatalysts that are (i) poor light absorption in visible regions and (ii) photoexcited charge separation and transportation in heterojunctions. These problems are solved by formation of heterojunctions between two or more semiconductors which enhance their photocatalytic activities. Effective charge transfer at the heterojunction is a key factor required to explore further as the already developed schemes have the major technicalities to address for the enhanced photoexcited charge production and separation via effective interface, without losing effective electrons required for boosting the rates of various reactions at the surface sites of the photocatalysts. This review gives an overview of photocatalytic activities, and construction of various types of heterojunctions between metal oxide-metal oxide, metal oxide-metal sulfide and metal sulfide-metal sulfide-sased heterostructures. The band gap adjustments and alignments in various types of emerging heterojunctions are explored and correlated to establish structure-photoactivity relationship and photostability of metal oxides and metal sulfides with established binary, ternary and quaternary composites. This study has paved the potential ways to design efficient heterojunction-based strategies for photocatalytic applications.

1. Introduction

The accessibility of renewable energy sources, clean water and environment are considered to be major challenges in recent years. The development of the industries and human society is strongly depended on fossil fuels which causes excessive emission of greenhouse gases and increases environmental pollution. Therefore, there is a need of development of environmentally friendly energy resources such as semiconductor-photocatalysis [1]. Thus, Photocatalysis is the process in which visible light having energy equal to or greater than its band gap energy is adsorbed on the surface of semiconductor catalyst (SC) which causes excitation and migration of electrons and holes to its conduction band and valence band. The reaction involves in this process is [2]:

 $SC + h\nu \rightarrow h^+ e^-$

 $\mathbf{h^+e^-} \rightarrow h_{VB}^+ + e_{CB}^-$ To obtain pollution free environment there are some treatments required such as; water splitting, dye degradation, CO₂ reduction and H₂O₂ production (Fig. 1). Firstly, Photocatalytic water

splitting is regarded as artificial photosynthesis because it is similar to the natural photosynthesis uses solar light by the green plants [3]. In this process, solar energy is converted into chemical energy while water splitting process promotes Gibbs free energy [4]. Generally, photocatalytic water splitting requires solar light, photoreactor, reactant (water) and photocatalyst to produce hydrogen [5]. The mechanism for photocatalytic water splitting for hydrogen production has four main processes which are (i) light harvesting (ii) charge excitation (iii) charge separation and transportation (iv) surface catalytic reactions [6]. This process starts with visible light irradiation having energy equal to or greater than band gap of the photocatalyst. The photocatalyst absorbs appropriate light energy and causes electronic transition and generates electron-hole pairs. The charges are separated and electrons are transferred from valence band to conduction band leaving the holes behind. The electrons and holes cause reduction and oxidation reaction with water and produce hydrogen and oxygen [7,8]. Contrarily, water splitting is an endothermic process [9] and requires source of energy to fulfill Gibbs free energy (ΔH° =238kjmol⁻¹ to rearrange the valence electrons for formation of H2 and O2 [10]. In order to produce one molecule of

E-mail address: asad_032@yahoo.com (A. Mumtaz).

^{*} Corresponding author.

hydrogen from water 2.458 eV energy is required. Since, two molecules of hydrogen are produced from water using four electrons and the energy will be required about 4.915 eV. These photons can be utilized by visible light with wavelength 504.5 nm to produce hydrogen [11,12]. When semiconductor uses sunlight higher than band gap energy then e-/h+ pairs are delocalized within semiconductor and causes electrons to attain internal equilibrium within energy level instead of across the band gap and these states are referred as Fermi levels. Under visible light illumination, electrons and holes are not generated by heat as the solar light is utilized as Gibbs free energy for photocatalytic water splitting [13,14]. The photocatalytic water splitting is represented in the following equations below:

$$2H^+$$
 + $2e^ \rightarrow$ $H_2E^{\circ}_{reduction} = 0.00V_{NHE}$
 H_2O + $2h^+$ \rightarrow $2H^+$ + $\frac{1}{2}O_2E^{\circ}_{avidation} = 1.23V_{NHE}$

Secondly, photodegradation is broken down of larger species into low molecular weight, non-toxic and smaller species chemically under solar light illumination. The mechanism involves absorption of photon energy which is greater than or equal to band gap energy of the photocatalyst. The excitation of electrons occurs from the valence band to the conduction band which leads to formation of electrons and hole pairs. The photoexcited holes and electrons interact with dye molecules and produces dye*. These unstable dyes convert to dye and dye radicals. These positive and negative radicals spontaneously decompose to the degradation products [15]. The photodegradation of organic dves is usually based on highly reactive OH radicals. These OH radicals are produced by the reaction of electrons and holes and the rate of reaction is expressed by Langmuir-Hinshelwood and Eley-Rideal mechanism $1/[P]_t=k_2t+1/[P]_0$ [16,17]. Thirdly, Photocatalytic CO₂ reduction mimics the natural photosynthesis in which solar light energy is used to convert CO2 into more reduced species such as; CO, HCOOH, HCHO, CH₃OH, CH₄ and C₂H₅OH [18,19]. Thermodynamics of CO₂ reduction involves redox reaction and positive Gibbs free energy values which is not favorable under standard conditions and requires energetically uphill [20,21]. It is non spontaneous process and requires an input of energy to proceed and is favorable at specific temperature and pressure conditions [22]. Therefore, the Gibbs free energy for CO₂ reduction to CO is 257kj/mol, HCOOH is 286kj/mol, HCHO is 522kj/mol, CH₃OH is 703kj/mol and C₂H₅OH is 818kj/mol [23]. Electrons are involved in the photoreduction of CO2 and band gap plays an important role. It takes place if the conduction band level is higher than reduction potential of CO₂ and valence band is more positive than oxidation potential [24].

The photoreduction of CO₂ involves following equations:

$$CO_{2} + e^{-} \rightarrow CO_{2}^{-} \quad E_{redox}^{\circ} = -1.9V$$
 $CO_{2} + H^{+} + 2e^{-} \rightarrow HCOO^{-} \quad E_{redox}^{\circ} = -0.49V$
 $CO_{2} + 2e^{-} + 2H^{+} \rightarrow CO \quad E_{redox}^{\circ} = -0.53V$
 $CO_{2} + 4e^{-} + 4H^{+} \rightarrow HCHO \quad E_{redox}^{\circ} = -0.48V$
 $CO_{2} + 6e^{-} + 6H^{+} \rightarrow CH_{3}OH \quad E_{redox}^{\circ} = -0.38V$
 $CO_{2} + 4e^{-} + 8H^{+} \rightarrow CH_{4} \quad E_{redox}^{\circ} = -0.24V$

Lastly, photocatalytic production of H_2O_2 is also governed by basic photocatalytic reaction principle. It can be generated through either a sequential two step single electron indirect process or one step two electron direct process route [25]. The indirect reduction process of photocatalytic H_2O_2 production involves production of superoxide radicals from one electron reduction of O_2 which further react with H^+ and form OH_2 radicals. This OH_2 undergoes one electron reduction and produce OH_2 . This OH_2 finally reacts with OH_2 and produce OH_2 product. Meanwhile, in the direct reduction process OL_2 would directly reacts with two OH_2 in and produce OH_2 product using two electrons for photoreduction. This process is uphill reaction with standard Gibbs free energy change is OH_2 model [26,27]. The reaction involves following equations:

$$O_2 + e^- \rightarrow O_2^-$$

$$O_2 + H^+ \rightarrow HO_2^-$$

$$HO_2^- + e^- \rightarrow HO_2^-$$

$$HO_2^- + H^+ \rightarrow H_2O_2$$

$$O_2 + 2H^+ + 2e^- \rightarrow H_2O_2$$

$$E_{redox}^e = 0.68V$$

 $2H_2O \,+\, 4H^+ \rightarrow O_2 \,+\, 4H^+$

Similarly, computational simulations were also applied to study the semiconductor-photocatalyst. The structure of the semiconductor can be studied the OPLS-2005 forcefield and low mode sampling logarithm [28]. The structures with lower energy window can be optimized by DFT and B3LYP [29]. The optical studies of the material can be calculated by different models of TD-DFT. The redox potential of the catalyst can be calculated by using DFT and TD-DFT with equation $E^{\circ}(x) = -\Delta G(x)/nF$

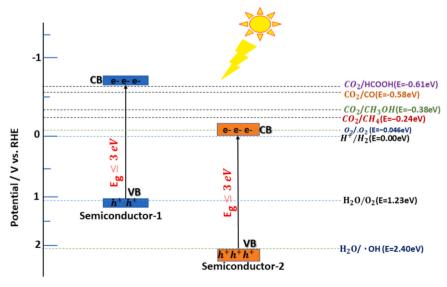


Fig. 1. Mechanism of Photocatalytic Water Splitting, Photodegradation of Dye, Photoreduction of CO₂ and Photocatalytic H₂O₂ production.

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There are some factors which affect the activity of the photocatalysts (i) the band structure of the semiconductor catalyst plays an important role to optimize the activity of the catalyst and usually band gap value is lied between 0.2eV-3.5 eV. The ideal value of band gap is typically concentration between 1.23 eV and 3.0 eV. (ii) Charge carrier excitation and separation is crucial part to enhance the photocatalytic activity of the material. When photogenerated charge carriers face any defect in the semiconductor they recombine and release energy due to coulombic forces. Therefore, charge separation is necessary during the development of the catalysts. (iii) the surface activity of the catalyst is also necessary for the favorable activity of the material. The surface activity is determined by quality and quantity of the active sites and surface morphology of the material [32]. Therefore, the design and development of photocatalyst should consider both factors to enhance the activity of the material. There are some methods that can be used to improve the activity of the materials. (1) Adjustment of the band gap structures by modulation of electronic configuration with doping (2) Structural medication of the materials by using significant synthesis method to control the morphology of the catalysts (3) The use of specific cocatalyst which creates of active sites, reduces activation energy of the reaction and provides sufficient system stability (4) Construction of heterojunction typically suppresses the charge recombination and increases the charge separation and considered to be the most effective method to improve the efficiency of the semiconductor photocatalysts

Generally, the heterojunction is an interface between two different semiconductors with unequal band structure leads to spatial band alignments [34,35]. There are three types of conventional heterojunctions: (a) Type-I (b) Type-II (c) Type-III. Type-I heterojunction (Fig. 2a) is known as Stradling gap. For this heterojunction, the conduction band (CB) of the semiconductor A are higher due to its lower work function than CB of the semiconductor B due to its higher work function and the valence band (VB) of the semiconductor A is lower than VB of the semiconductor B. Therefore, under solar light illumination, the electrons accumulate in CB and holes accumulate in VB of semiconductor B. Since, the electrons and holes accumulated on the same semiconductor, the electron-hole pairs cannot be separated effectively

due to higher probability of recombination rates and redox reaction takes place at lower reduction and oxidation potential and reducing the redox ability of heterojunction photocatalysts significantly [36]. For Type-II heterojunction (Fig. 2b) or staggered gap, the CB and VB levels of the semiconductor A are higher than the corresponding CB and VB levels of semiconductor B, respectively. As a result, photogenerated electrons will migrate to semiconductor B and holes will transfer to semiconductor A under light illumination leads to electron-hole pair separation. The redox ability of type-II heterojunction will also be reduced because the reduction potential and oxidation potential take place at lower reduction and oxidation potential [37,38]. Although type-II is ideal for charge separation but the charge separation takes place at lower reduction potential which is unfavorable for photocatalytic reactions. As the electrons are accumulated on CB of semiconductor B and holes are accumulated on semiconductor A with weak reduction and oxidation potential leads to impair driving force for specific photocatalytic reactions thermodynamically. Similarly, the repulsion between electron and electrons of both CB and repulsion between holes of both VB impedes the spatial transfer of charge carriers. The electrostatic attraction between electrons and holes hinders the transfer of electrons and holes from one semiconductor to another. So, the charge transfer in type-II heterojunction is hard to predict and fails to separate the electrons and holes spatially. Besides this, the transfer mode weakens the redox ability of the photocatalytic reactions. Type-III heterojunction (Fig. 2c) or broken gap is similar to type-II heterojunction except that the staggered gap becomes so extreme that the band gaps of both the semiconductors do not overlap leads to separation and migration of electron-hole pairs impossible and make it unsuitable for enhancing the separation of electron-hole pairs [39]. Among the conventional heterojunction, type-II heterojunction is the most effective heterojunction to enhance the photocatalytic activity due to its favorable structure for spatial separation of electron-hole pairs. But there are some limitations for the development of type-II heterojunction. As the redox reactions take place with lower reduction and oxidation potentials it suppresses the redox ability of the semiconductor photocatalysts. Moreover, the migration of electrons from semiconductor A to electron rich CB of semiconductor B and holes migrate from semiconductor B to holes rich VB of semiconductor A leads to electrostatic repulsion

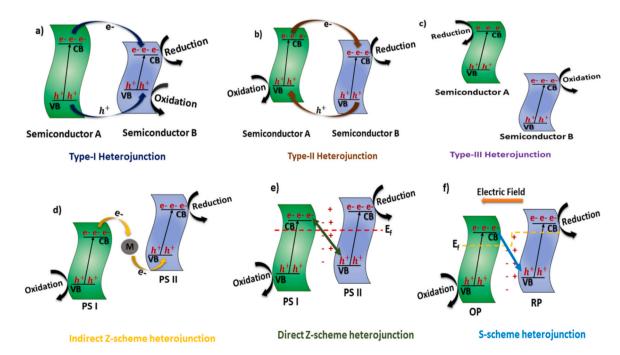


Fig. 2. Schematic Illustration of different types of separation of electron-hole pairs in light responsive heterojunction photocatalysts: a) Type-II, b) Type-III, d) Indirect Z-scheme, e) Direct Z-scheme, and f) S-scheme heterojunctions.

between electrons and electrons as well as holes and holes and make them unfavorable heterojunction. To overcome the aforementioned problem, Z scheme heterojunction was introduced by Bard in 1979 to enhance the redox ability of the heterojunction systems. The conventional Z scheme heterojunction consists of two photocatalyst systems PS I, PS II semiconductors and acceptor/donor (A/D) pairs. During the reactions the electrons from the CB of PS II transfer to the VB of PS I through acceptor/donor pairs. Here, A is reduced to D by reacting with the electrons from the CB of PS II. D is oxidized to A by the holes from VB of PS I. The electrons are accumulated on PS I with higher reduction potential and holes are accumulated on PS II with higher oxidation potential leads to higher redox ability. But it is feasible for liquid mediums only, produces side products, low light harvesting ability and pH sensitivity limiting its applications. Therefore, solid state Z scheme heterojunction (Fig. 2d) was developed in 2006 by Tada in which solid electron mediator was used between PS I and PS II semiconductor systems. Under light illumination, the electrons were transferred from CB of PS II to VB of PS I through electron mediator and electrons and holes are separated at higher reduction potential and oxidation potential with optimized redox ability. It is suitable in solid, liquid ang gas phases for photocatalytic applications [40]. But they faced some problems which are remained unsolved. It is hard to control the synthesis process as the majority of conductor particles does not lie exactly between the photocatalyst and randomly lie on the surface of the photocatalysts. Instead of acting like electron mediator they started to act like cocatalyst. The noble metals are conductors and usually absorb light and starting to compete with the photocatalysts in light harvesting and reduces the light harvesting ability of the photocatalysts. To align the Fermi levels the Schottky barrier is formed between metal and semiconductors and suppresses the flow of electrons from both semiconductors to metal leads to band arises at the interface and asserted charge transfer does not take place. In 2013 Wang group prepared direct Z scheme heterojunction (Fig. 2e) without the solid-state electron mediator. Direct Z scheme has staggered bands which mimics the natural photosynthesis process. This heterojunction consists of two semiconductors PS I and PS II. When both semiconductors with different energy levels come in contact the Fermi levels make an equilibrium. The band edge bending occurs at the interface of both semiconductors and produces electrostatic attraction which accelerates the recombination of electrons of PC I electrons and PC II holes. The electrons in the CB of PC II and holes in the VB of PC I lead to reduction and oxidation of water with higher redox potentials. The main advantages of this type of heterojunction are that electrons and holes are separated at higher reduction and oxidation potentials without expensive electron mediator and cost of the photocatalyst is comparable to type-II heterojunction photocatalysts. Simultaneously, the migration of electrons from CB of PS II to VB of PS I is easier due to electrostatic attraction between electron and hole pairs [41,42]. But the charge transfer mechanism of the direct Z scheme heterojunction lacks experimental evidences and limits its applications. By keeping the idea of direct Z scheme in view the concept of S scheme heterojunction was introduced. The S scheme heterojunction (Fig. 2f) basically consists of two semiconductors reduced photocatalyst (RP) and oxidation photocatalyst (OP). The RP has higher CB, VB, Fermi level and smaller work function than OP. When RP and OP comes in contact the electrons in RP with higher Fermi level will migrate to the OP with lower Fermi level at the interface [43]. The RP loses electrons and becomes positively charged. Meanwhile, the OP gains electrons and becomes negatively charged leads to upward and downward band bending at the interface of OP and RP. Concurrently, a built-in electric field is produced which is directed from RP to OP and photogenerated electrons are transferred from CB of OP to VB of RP under light irradiation [44]. Moreover, the coulombic attraction between electrons of OP and holes of RP and band bending between them favors the charge transfer [45]. Contrarily, coulombic repulsion, band bending and built-in electric field inhibit the electron transfer from the CB of RP to CB of OP. The powerful electrons and holes are reserved in CB and VB of RP and OP and weak charge

carriers are recombined leads to strong redox ability. The charge transfer path is step-like macroscopically, therefore named as S scheme heterojunction [46,47]. The main disadvantages od S scheme heterojunctions are: (a) they are limited to powder photocatalysts (b) Their applications in the field of photo electrochemistry are limited (c) They are usually constructed using the n-type semiconductors having suitable band structures and Fermi level positions [48]. The specific conditions are required for the formation of specific types of heterojunctions. They include: (i) Spatial band alignment (ii) Compatible lattice matching (iii) High quality interface with minimal defects with less recombination of charge carriers (iv) Chemical and photo stability (v) Controlled Morphology (vi) Energy level alignments [49]. The common characterization methods to study the formation of heterojunction are X-ray photoelectron spectroscopy (XPS), Kelvin probe force microscopy (KPFM), DFT calculation and electron paramagnetic resonance (EPR). XPS detect the energy density and electron binding energy of both semiconductors using different conditions and parameters. In these methods, under light illumination the hybridization of semiconductors takes place, interfacial charge transfer occurs which increase the electron density and shifting the binding energy of both semiconductors leads to identify the formation of type of heterojunction [50]. Similarly, KPFM measures the surface potentials and corelated the charges on the semiconductors with the Fermi levels [51]. DFT calculations provides the information about work functions and density of states (DOS). Upon charge transfer between the semiconductors charge density difference is produced which shows the accumulation and depletion of electrons in the semiconductor photocatalyst and demonstrates the electron transfer from one semiconductor to other [52,53]. EPR method used radicals which are produced by photoreduction of O2 and photooxidation of water. The higher redox powers stronger will be the EPR signals. Therefore, the composite of semiconductors shows stronger EPR signals than individual semiconductors show the formation of heterojunction and also demonstrate the type of heterojunction [54]. These heterojunctions have various applications: Type-I heterojunction has Efficient charge confinement and suitable for those applications in which electrons and holes should be accumulated in one material. They are applicable for LEDs and Laser diodes. But they have limited charge separation and higher charge recombination. Type-II heterojunction has efficient and spatial charge separation with reduced charge recombination. They are used for photocatalysis, photovoltaics and photodetectors. But they have lower absorption efficiency and interface quality. P-n heterojunction has built-in electric field and can be used in solar cells, photodetectors and diodes. Schottky junctions has efficient charge separation at metal and semiconductor interface and used in Schottky diodes. But they face metal and semiconductor interface have high rate of recombination and have very limited choice of metals.

In this review heterojunction in the metal oxide and metal sulfidebased composites with their various photocatalytic activities are discussed. These composites have following advantages: (a) They have higher surface area which provides more active sites for the reactions. (b) they have optimal band gap (c) Balanced charge separation and transfer upon heterojunction formation (c) Have higher chemical and thermal stability (d) They are abundant in nature, non-toxic and cost effective (e) Higher visible light absorption spectrum and show surface plasmon resonance (SPR) effect [55-57]. The photo electrocatalysts are also discussed with the photocatalysts due to following reasons: (1) photo electrocatalysts incorporate the external electric field which help to separate the charge carriers and reduces the recombination (2) The applied voltage facilitates the better control over the reaction pathways and produces the desired products (3) The external electric field lowers the activation energy of the reactions compared to photocatalytic reactions (4) Help to prevent photo corrosion, increase stability and longevity [58,59]. To be remain focused, authors have emphasized on the mechanistic study of different type of heterojunctions along with some representative applications for in depth investigations. Moreover, some representative examples are also required to correlate and

establish the problems associated with the different hetrojunction schemes and to analyze them in exploring the future strategies. Therefore, metal oxide-metal oxide, metal oxide-metal sulfide, and metal sulfide-metal sulfide-based heterojunctions were selected as representative to be remain focused. Otherwise, Metal Carbides, Metal Nitrides, Metal Phosphides and/or other semiconductors may also be included in the review, that may increase the width of the article but the main strategies may remain same. So, the objectives of the review articles were fulfilled by the chosen representative metal oxides and metal sulfides.

This review represents the appreciation of recent efforts and work in constructing various types of heterojunctions in metal oxide based and metal sulfide-based composites and highlights their applications in water splitting, photoreduction of CO_2 , photodegradation of dyes and photocatalytic H_2O_2 production. The above explained four types of heterojunctions and their applications as well as role of nanopyrophosphate in the catalyst are reviewed. Furthermore, we are suggesting three different kinds of novel schemes of ternary composites in this review which are discussed in the conclusive discussion of each portion and would be helpful to develop novel and highly effective heterojunctions in future. We hope that this review provides useful information on synthesis of various heterojunction in binary and ternary composites of metal oxide and metal sulfide and their applications in photocatalysis.

2. Metal oxide-metal oxide based composite

Metal oxides have excellent chemical stability, a wide range of band gaps and suitable band gap positions [60]. Normally, VB and CB of metal oxides have O 2p and transition metal s, p & d characters. The metal oxides in which metals have s orbital and high ionic character 2p have large band gaps. The metals oxides in which metals has d^n electronic configuration possess smaller band gap. By combining these two different kinds of metal oxides binary and ternary oxides are formed with adjustment the band gap position of both metals [61]. All types of mechanisms for adjustment of band gap positions and charge transfer in metal oxide heterojunctions are explained by using representative examples below.

2.1. Type-II heterojunction

The Fermi level, coulombic forces and work functions play an important role to form specific type of heterojunction. The type-II het-

erojunction consists of two semiconductors. When two semiconductors come in contact the charge transfer takes place to build type-II heterojunction due to difference of Fermi level. The electrons will move from semiconductor with higher Fermi level and lower function to the semiconductor with lower Fermi level and higher work function. The movement of electrons leads to create electric field at the interface due to coulombic forces between the charges and ions of the donor or acceptor atoms. These electric fields cause the energy bands to bend and Fermi levels make an equilibrium forming the staggered band structure [62,63]. Chai et. al., reported a three-dimensional urchin-like photoanode TiO2@Fe2O3 was prepared by combination of colloid sphere template, atomic layer deposition and hydrothermal method. The Co-Pi was used as an oxidation co-catalyst showing the significant increase in its photocurrent density from 1.58 mA/cm² to 3.6 mA/cm² at 1.23 V and 1.6 V vs RHE (see Fig. 3a-b). The mechanism for electron transfer involves two n-type semiconductors. The band gap of TiO_2 and Fe_2O_3 is 3.2 eV and 2.2 eV containing CB values of both semiconductors are 0.18 and 0.46 eV and VB values are 3.38 and 2.66 eV. As CB values of Fe₂O₃ is more negative and VB values of TiO2 is more positive, than electrons will travel from Fe₂O₃ to TiO₂ conduction band and holes will travel in opposite directions. In this heterojunction when light falls on photoanode the electrons in the valence band become excited and migrate to conduction band of both semiconductors leaving holes behind (Fig. 3a). The Fermi-level of both semiconductors got adjusted due to internal electric field produced by movement of charge carriers and electrons will travel from CB of Fe₂O₃ to TiO₂ with lower reduction potential and reach to Pt cathode and cause reduction of water to produce hydrogen. Meanwhile, holes in the VB of TiO2 will travel to VB of Fe2O3 and quenched by oxidation catalyst Co-Pi and lower overpotential of oxidation of water and increase the oxidation kinetics of Fe₂O₃/Fe₂TiO₅

In the same way, Zhang et. al., synthesized p-n heterojunction of p-CuO (E_g =1.34 eV) and n-ZnO (E_g =3.14 eV) by combination of one step electrodeposition and thermal treatment methods on cauliflower shaped photocathode. The electrons would travel from p to n semiconductor forming a p-n junction and the type-II mechanism was formed as electrons and holes travel in opposite directions [65]. Pihosh et. al., prepared n-n and type-II heterojunction with WO₃ (E_g =2.71 eV) nanorods and BiVO₄ (E_g =2.4 eV) thin layers and co-catalyst Co-Pi by glancing angle deposition and normal physical sputtering on Iodine doped tin oxide (ITO) substrate with photocurrent density of 3.2 and 5.1 mA/cm² at 1.23 V versus reversible hydrogen electrode (RHE) under simulated

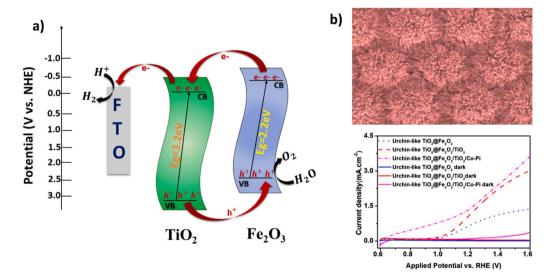


Fig. 3. a) Mechanism of charge transfer of TiO_2/Fe_2O_3 b) Photocurrent density of Urchin-like $TiO2@Fe_2O_3$ in light & dark. Reproduced with permission and copyright 2018, Elsevier [64].

solar light 100 and 200 mW/cm² in 0.5 M Na_2SO_4 electrolyte [66]. Castro et. al., synthesized WO_3 and TiO_2 heterostructure by hydrothermal method with different concentrations of WO_3 (20 %, 40 %, 80 %) and 40 % hybrid shows highest current density 210 μ A/ cm² and less charge carrier recombination. The electrons would be shifted to CB of WO_3 that moves to the Pt cathode for reduction of water and holes in opposite directions, building type-II mechanism [67].

Hao et. al., synthesized a photoanode of n-type TiO₂ and p-type Ag₂O $(E_g = 3.0 \text{ eV})$ by hydrothermal and chemical bath deposition method having photocurrent density 1.61 mA/cm² at 1.23 V vs. NHE with 0.5 M Na₂SO₄ electrolyte under visible light irradiation. The mechanism is p-n and type-II heterojunction [68]. Yao et. al., used chemical bath deposition (CBD) method to synthesize TiO_2 and p-Cu₂O (E_g =2.1 eV) core/shell nanowire arrays. It showed 2.5 mA/cm² photocurrent density 2.5 times higher than pure TiO2 nanowires and produced H2 32 µmol/hcm² which is 1.7 times higher than pure form. The photoexcited electrons are transferred from CB of Cu2O to TiO2 and holes in opposite directions representing Type-II mechanism [69]. Wang et, al., organized heterostructure of rutile TiO2 nanorods and Nano bowls (NR@NB) arrays by hydrothermal method forming type-II heterojunction. The photocurrent density was 1.24 mA/cm² at 1.23 V with RHE two times of bare TiO2 NRs on FTO [70]. Suleiman et. al., synthesized a photocatalyst of TiO_2 /ZnO (E_g =3.2 eV) by wet chemical method for degradation of azo-dye orange II in water solution which is 53 % under UV light illumination and 72 % under visible light illumination. It is due to higher surface illumination under light, effective charge separation and finer contact which type-II between both semiconductors [71]. Achouri et. al., prepared ZnO/Fe₂O₃ heterostructure by wet chemical method (sol-gel method). Iron oxide has narrow band gap (1.9-2.2 eV) and ZnO has broader band gap (3.2 eV) and their composite have better charge separation and increased degradation efficiency of salicylic acid (SA) up to 60 % under UV light exposition in 1 hour [72]. A ternary composite of ZnO/ZnFe₂O₄/TiO₂ was prepared by hydrothermal method with excellent photocatalytic performances of 96.32 % of methylene blue (MB) degradation due to spatial charge transportation. For the photodegradation OH species produced by visible light irradiation of the photocatalysts are responsible for photodegradation of the contaminants. The CB and VB of the semiconductors should be placed in such a way that reduction potentials of O₂ and oxidation potentials of OH species are in the scope of the band gaps thermodynamically [73]. ZnO and TiO₂ have wider band gap ZnFe₂O₄ will be used for degradation and other two semiconductor photocatalysts would contribute individually in the ZnFe₂O₄. Under light illumination, electrons will migrate from the VB to the CB of the semiconductors leaving the holes behind in the VB. Because the potential of ZnFe₂O₄ is more negative than ZnO and TiO₂, the electrons of ZnFe₂O₄ will travel to TiO2 and ZnO. This process reduces the recombination of electrons and holes. The electrons react with O₂ to form O₂ radicals. The O₂ radical reacts with H⁺ to form H₂O₂ and further reacts with electrons to form OH species for degradation process [74]. Iqbal et. al., developed a p-n heterojunction of ZnFe₂O₄/TiO₂ with (1:1), (1:2) and (2:1) by hydrothermal method with pre-annealing treatment of ZnFe₂O₄ at 900°C and sol-gel method followed by post-annealing of heterostructure at 500°C for the reduction of CO₂ to methanol. The photocatalytic production of methanol is 693.31 µmol (g cat)⁻¹ with 1:1 due to lower band gap, higher surface area, more active sites, more crystallinity, maximum visible light absorption, maximum charge separation and transportation for CO2 reduction. Here electrons are transferred from CB of ZnFe₂O₄ to TiO₂ and holes in opposite direction and reduction potential of methanol is near CB of TiO₂ [75].

2.2. Direct Z-scheme Heterojunction

In the case of direct Z scheme, the backward reactions and shielding effect in the heterojunction are suppressed due to absence of electron

mediator. When two semiconductors come in contact the work function difference and formation of electric field are significantly necessary for photogenerated charge separation and transfer [76]. One semiconductor with higher CB and VB and lower work function comes in contact with the semiconductor having lower CB and VB and higher work function leads to formation of internal field and favors Z heterojunction [77]. The factors internal electric field, extra potential barrier induced by band bending and coulombic repulsion inhibit the transfer of electrons from CB of one semiconductor to other. Similarly, the internal electric field also suppresses the transfer of electrons from CB to CB of semiconductors leading to formation of Z scheme heterojunction [78-81]. Zhou et. al., fabricated open bird-nest structured (Fig. 4a) ZnO-TiO2 by hydrothermal approach and controlled spin-coating method to solve problems like poor light harvesting and sluggish carriers' kinetics. The photoanode have photocurrent density 1.05 mA/cm² at 0.6 V and 2.75 mA/cm² at 1.23 V vs RHE which 4.32 and 2.27 times higher than TiO₂ and 1.98 and 1.38times higher than sealed CS ZnO-TiO₂ photoanode. Under the light illumination excitation of electrons took place and transferred from VB to their CB. As the CB value of ZnO is -0.17 eV and that of TiO2 is -0.20 eV then electrons will transfer from more negative to less negative. But the electrons travel from CB of ZnO to VB of TiO2 due formation of Schottky barrier and electrons of TiO₂ produced hydrogen with higher reduction potential and holes in the VB of ZnO produced oxygen with higher oxidation potential. So, Schottky junction has managed better charge separation than type-II junction due to reduction and oxidation of water at higher reduction and oxidation potential. Due to the formation of the Z-shape this mechanism is Z (Fig. 4b) mechanisms [82].

Dhiman et. al., synthesized dual function ZnO/Fe₂O₃ heterostructure via sol-gel method and spin coating method for degradation of sulfamethoxazole (SMA) and detection of dopamine (DA). The composite degraded SMA upto 95.2 % under visible light exposure in 90 minutes with limit of detection and limit of quantification for S2 modified surface of dopamine is 0.18 μM and 0.62 μM and are calculated as: LOD=3xS/m and LOQ=10xS/m [83]. Chen et. al., synthesized ZnO-WO3 composite by in-situ solvothermal method having 1,5,10 and 15 ratios in which Zn-W-5 under light illumination have lowest onset potential 0.36 V vs. RHE and highest photocurrent density 2.39 mA/cm² at 1.23 V vs. RHE 2.13 times higher than ZnO NRs and IPCE% up to 84 %. The charge transfer mechanism followed in this composite is solid-state direct z-scheme (Fig. 5a-b) as the band edge of ZnO bend downward and WO₃ bend upward cause recombination of electrons and holes. Meanwhile, electrons of ZnO and holes of WO3 cause reduction and oxidation of water. Piezoelectric PEC water splitting is also generated with 300-1000 rpm rate, giving 3.09 mA/cm² at 1.23 V vs. RHE photocurrent density and 0.21 V lowest onset potential [84].

A ternary photoanode ZnO/AgI/WO3 was developed by hydrothermal method having double direct z-scheme activities and degradation of methylene blue (MB) occurred up to 85.2 % under visible light. PL spectra of ternary composite show lowest emission peaks which means it has lowest recombination of electrons and DRS spectra shows composite has lowest band gap which is 2.79 eV. Here, the Z-scheme shows electron-holes of WO3-CB and ZnO-VB and AgI-CB and WO3-VB recombine while electrons of AgI-CB cause reduction and holes of WO₃-VB cause oxidation [85]. CuO quantum dots (QDs)/WO₃ NS also formed a direct Z-scheme by self-assembly strategy loading of 0D CuO QDs on 2D WO3 NS [86]. Whereas, a heterostructure of Cu2O and TiO2 with direct Z-scheme heterojunction was reported by solvothermal method and stabilizing Cu₂O from photo corrosion to reduce CO₂ to methanol and ethanol. The photocatalytic conversion of CO2 to CO is 2.11µmol (g cat)⁻¹ four times higher than pure Cu₂O. The band alignment and energy differences at the interface of the composite are usually determined by XPS and DRUV. If the composite follows the Type-II (staggered gap) band, the energetic CB favors the reduction of CO₂ via photogenerated electrons. After considering the energy difference between CB and Fermi level of TiO2 as well as VB and Fermi level of Cu2O do not remain constant before and after contact. The energy difference

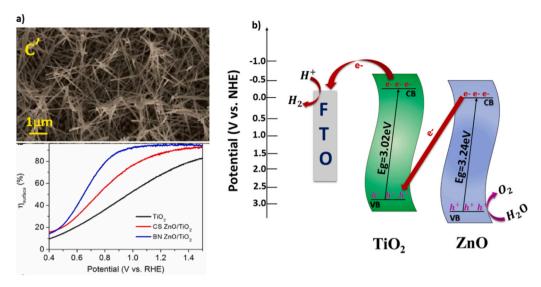


Fig. 4. a) Open bird nest structured TiO2/ZnO b) Mechanism of charge transfer of TiO2/ZnO. Reproduced with permission [82]. Copyright 2014, Elsevier.

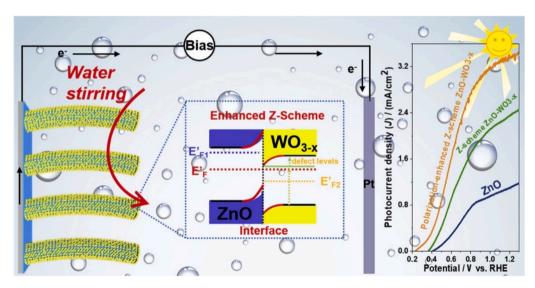


Fig. 5. Schematic diagram of polarization process of ZnO and PE-PEC process with energy band diagram of Zn-W-m. Reproduced with permission [84]. Copyright 2019, Elsevier.

between the CB of TiO_2 and VB of Cu_2O before contact is 0.62 eV. This energy difference between the CB of TiO_2 and VB of Cu_2O is favorable for separation of photogenerated electron and hole pairs through direct Z scheme heterojunction due to overlap of energy levels upon p-n heterojunction formation. In order to make the reduction of CO_2 feasible, Z scheme pathway is followed and anodic reaction takes place in the Cu_2O surface as CB level of Cu_2O is less negative than CO_2 reduction potential. So, to make CO_2 reduction thermodynamically possible holes are scavenged by water because accumulation of electrons in CB of Cu_2O leads to production of CO [87].

2.3. Indirect Z-scheme Heterojunction

In this type of heterojunction electron mediator (Ag, Au and Pt) is used between the two semiconductors reduce the charge transfer length and accelerate the charge transfer. It consists of three components and the Fermi level of one semiconductor is higher than other semiconductor with lowest Fermi level of the metal mediator. All three components come in contact and charges redistribute at the interface having different Fermi levels. To align the Fermi levels, the electrons will

transfer from both semiconductors to the metal surface. Simultaneously, band bending takes place at the interface of semiconductor and metal forming the Schottky barrier and suppress the flow of electrons from both semiconductors to metal. Therefore, electrons with lower CB transfer to metal and recombine with the holes of VB of another semiconductor [42,88,89]. Tahir et. al., prepared a solid-state Z-heterojunction consisting of ZnFe₂O₄ (E_g=1.99 eV), Ag and TiO₂ photocatalysts by hydrothermal, photo-deposition and solvothermal method (Fig. 6a-b). The photocatalytic activity of nanocomposite was improved by fabrication of Ag nanoparticles as electron mediator and obtained highest CO amount of 1025µmolg-1cat-1 and hydrocarbons like CH₄, CH₃OH and C₂H₆ with amount of 132, 30.8 and 19.1µmolg⁻¹cat⁻¹(Fig. 6b). Under light illumination, the electrons got excited by absorption of photons and migrated from their VB to CB. The CB of TiO₂ is much lower than CB of ZnFe₂O₄ and close to VB of ZnFe₂O₄ and Ag in between act as electron mediator. The electrons from CB of TiO2 would transfer through Ag forming an Ohmic barrier to VB of ZnFe₂O₄ and cause reduction and holes in VB of TiO₂ cause oxidation of CO₂ to form CO and CH₄ (Fig. 6a) [90].

A ternary nanostructure of α-Fe₂O₃/Au/TiO₂ photoanode was

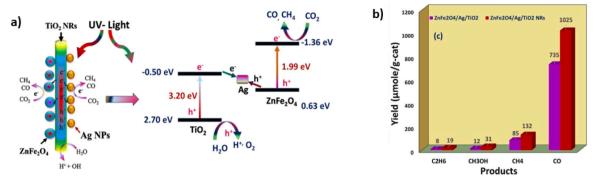


Fig. 6. a) Schematic representation of charge transfer in ZnFe₂O₄/Ag/TiO₂ nanocomposite, b) Performance comparison of nanoparticles and nanorods of nanocomposite catalyst. Reproduced with permission [90]. Copyright 2019, Elsevier.

developed by hydrothermal and pulsed laser deposition method giving photocurrent density 1.05 mA/cm² at 1.23 V vs. RHE which is 4.2 times greater than bare α-Fe₂O₃. This increase in photocatalytic activity is due to formation of heterojunction between Fe₂O₃ and TiO₂ by Au noble metal which acts as electron mediator and making it a solid state Zscheme heterojunction [91]. Also, a solid-state z scheme heterojunction of TiO_{2-x}/Cu/ZnO was synthesized by atomic layer deposition (ALD) and spray pyrolysis method. In this process, upon light illumination, the incident light penetrates through the ZnO layer and stimulated the electrons from its VB to the CB and the incident light is transformed to scattered light. If the ZnO layer is not present then most of the incident light is bled off but the incident light is repeatedly scattered between ZnO layer and Cu/TiO2 layer. The scattered light from ZnO layer is stimulates the Cu nanoparticles and electrons are generated from resonance collective oscillation. The band gap energy values of ZnO and TiO₂ were calculated which clearly demonstrated that the electrons will transfer from CB of TiO2 to Cu as the Fermi level of Cu is more positive than CB of TiO2. Similarly, the Cu metal acts as trap and electron mediator to capture electrons and facilitate the strong electron delocalization. The Fermi level of Cu is lower than VB of ZnO the trapped electrons will eventually be transferred from Cu to the VB of ZnO and holes of ZnO will be quenched. In this way, the photogenerated electrons and holes are separated and reduction of ZnO electrons takes place to produce hydrogen with higher reduction potential ability that led to formation of solid-state Z scheme heterojunction mechanism. Noticeably, the surface plasmon resonance (SPR) effect of Cu between TiO2 and ZnO enhances photocatalytic production of hydrogen which is 342.0 μ molg⁻¹ h^{-1} [92]. Similarly, a heterostructure of Ag₂O/Ag/amorphous-TiO₂ exhibited solid-state or indirect Z scheme by using stober method and stirring. It shows enhanced photocatalytic activity of nitrogen dioxide with photocurrent value of 28.2 nA. The mechanism involves migration of electrons from CB of Ag₂O to Ag making Schottky barrier and finally to VB of TiO2 and electrons in CB of TiO2 cause reduction and holes of Ag₂O cause oxidation of water due to surface plasmon resonance effect (SPR) of Ag between TiO2 and Ag2O [93]. While, Ag-Fe₂O₃-TiO₂ heterojunction was developed for photocatalytic degradation of organic dye Rh B by condensation reflux and mild-hydrolysis hydrothermal method. Ag showed localized SPR effect having highest apparent kinetic constant at 0.027min⁻¹ with recombination of electrons of TiO2 and holes of Fe2O3 through Ag. The electrons in CB of Fe₂O₃ show reduction and holes of VB of TiO₂ show oxidation [94].

2.4. S-scheme Heterojunction

A step scheme heterojunction has OP and RP with staggered band structure but a completely different charge transfer route than type-II heterojunction. The electrons are accumulated in the CB of RP and holes in the VB of OP and useless electrons and holes of OP and RP are recombined. RP has a higher CB and smaller work function than OP.

When both semiconductors come in contact, the electrons in the RP diffuse into OP creating the depletion layer and accumulation layer at the interface [95,96]. Concurrently, the internal electric field directed from RP to OP and electrons are transferred in opposite directions [97]. When both semiconductors come in contact the Fermi level form a curved shape and band bending occurs for transfer of electrons from CB of OP to VB of RP to recombine under the columbic attraction between electrons and holes [98–100]. An S-scheme based photoanode of 2D/2D TiO₂ and Bi₂O₃ was established by using hydrothermal methods. Where, the face to face minimized the distance for migration of charge carriers which is very helpful for production of H₂ 12.08µmol/g/h (Fig. 7a-b) by extending the lifetime of charge carriers with strong redox abilities. The charge transfer mechanism between 2D/2D TiO2/Bi2O3 photocatalysts is carried out by keeping one semiconductor as Reduction Photoanode (RP) and another as oxidation photoanode (OR). The band gap of TiO2 is 3.2 eV with conduction band value and valence band values as 0.05 eV and n-type semiconductor. The band gap of Bi₂O₃ is 2.72 eV having CB and VB values as 0.02 eV and 2.70 eV and act as n-type semiconductor. Under light illumination the electrons in the VB of both semiconductors became excitation and migrated from VB to their CB. The Fermi-level of both semiconductors is below CB and comes in equilibrium due to formation of interface and internal electric field. The electrons travel from CB of Bi₂O₃ to VB of TiO₂ to remove non-beneficial electrons and holes while the electrons in the CB of TiO2 reduce water to H2 with higher reduction potential. The holes in VB of Bi₂O₃ oxidize water to O₂ with higher oxidation potential (Fig. 7a). Here the type-II mechanism is not followed because it does not separate the useless electrons and gives lower activity with reduced redox potential. So the mechanism which followed to increase the production of H₂ in s-scheme heterojunction Γ1011.

The photogenerated electrons in CB of ZnMn₂O₄ and holes in the VB of ZnO are useful and cause reduction and oxidation with higher reduction potential and higher oxidation potential showing S-scheme mechanism [102]. Another S-scheme based ZnO/WO3 heterojunction showed highest photocatalytic activity of $6788 \mu mol/Lh$ of the H_2O_2 and sequentially 2.57 mA/cm² photocurrent density was observed. The electrons after excitation of WO₃ recombines with holes of ZnO leaving the electrons of ZnO for reduction of O2 leads to H2O2 formation while holes of WO₃ causes oxidation (same as shown in Fig. 4a). To get the in-depth understanding of photogenerated charge carriers transfer in the S-scheme heterojunction, electron paramagnetic resonance (EPR) measurement was studied by using 5,5-dimethyl-1-pyrrolidine N-oxide (DMPO) as a radical trapper. It is observed that DMPO-.O₂ signals of ZnO are stronger than WO3 because the electrons on the CB of ZnO hava stronger reduction potential than WO3. Similarly, PL spectra clearly depicts that the composite has smaller wavelength than the ZnO and WO3 shows that the photogenerated charge carriers have low recombination and higher charge carrier separation in the composite. The weaker signals of PL are caused by the combination of less powerful

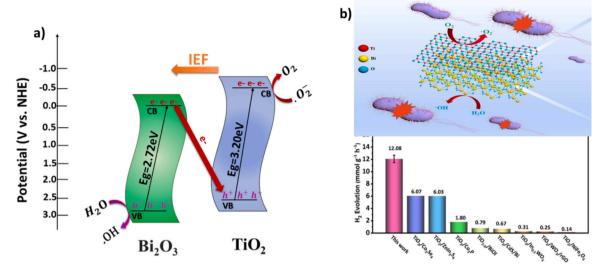


Fig. 7. a) Mechanism of charge transfer of Bi₂O₃ and TiO₂ b) Production of H₂ at different concentrations of TiO₂/Bi₂O₃ [101]. Copyright 2022, Elsevier.

electron and hole pairs in the composite within S scheme heterojunction. The higher separation of charge carrier efficiency and photosensitivity of the ZnO/WO₃ composite could be attributed to formation of S scheme heterojunction and enhance the production of H_2O_2 which is 6788 µmol L⁻¹ h⁻¹ [103]. Also, WO₃/Ag/ZnO by spray pyrolysis technique showed s-scheme heterojunction with Ag as an electron mediator. The composite provides degradation of cephalexin (CPX) up to 98.8 % at rotational speed of 180 rpm and solution flow rate is 1.0 L/min with light intensity 11 mW/cm² at pH 6. Upon photoexcitation, internal electric field is produced making Fermi-level at equilibrium which causes recombination of electrons of Ag/WO₃ and holes of ZnO while reduction H₂O to OH radical occurs by electrons of ZnO cause degradation of CPX and holes of Ag/WO₃ causes oxidation involves in other degradations [104]. Similarly, a ternary nanocomposite of ZnO-V₂O₅-WO₃ in Fig. 8 showed dual s-scheme mechanism having highest photocatalytic activities due to useful electrons of ZnO and V2O5 and holes of WO3 for reduction and oxidation at their surface active sites. The Raman studies showed that composite has oxygen vacancies that support fast charge separation and lower recombination, and UV-Visible studies showed the band gap of the composite was 2.63 eV. Furthermore, the photocatalytic activity was measured by degradation of cresol red (CR), rhodamine B (RB), methyl orange (MO), safranin-O (SO) and methyl red was 67.0 %, 86.6 %, 98.0 %, 98.0 %, 76.8 % and 99 % under visible light [105].

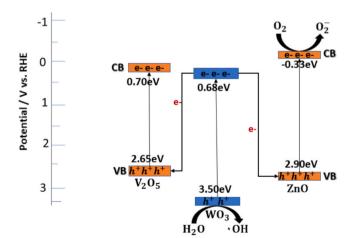


Fig. 8. Schematic representation of Dual S-scheme heterojunction in ZnO- V_2O_5 - WO_3 ternary composite. Reproduced with permission [105]. Copyright 2021, Elsevier.

Dual s-scheme heterojunction of Ga₂O₃/ZnO/WO₃ was synthesized by electrospinning method for degradation of Rh B. The photoexcited useless electrons of ZnO and WO3 are captured and electrons in the CB of Ga₂O₃ with band gap 4.9 eV involve in reduction while holes of WO₃ involve in oxidation which increases photocatalytic degradation of Rh B [106]. Floatable composite photocatalysts are synthesized by immobilizing the TiO₂ and Bi₂O₃ on a light weight polystyrene sphere via hydrothermal and photodeposition methods. This floatable photocatalyst is solar transparent and enhances the contact between reactants and photocatalysts. The photocatalyst produces an enhanced yield of H2O2 about $1.15~\mathrm{mM}~\mathrm{h}^{-1}$ by following the step scheme mechanism between TiO₂ and Bi₂O₃ [107]. There are a number of reasons which cause it to increase the activity of the binary or ternary composite. They include specific surface area of host layer, charge carrier diffusion distance, light harvesting efficiency, charge transfer and separation ability, presence or absence of co-catalyst, morphology of host layer, thickness of the guest layer which decides distance which is required for charge carriers to transfer from one layer to other, synthesis method, type of electrolyte, SPR effect of co-catalyst if used, band alignment, band gap, adjustment of Fermi-levels, type of formation of heterojunction. From above explained examples WO₃/BiVO₄ (p-n heterojunction) formed by glancing angle deposition and normal physical sputtering shows highest photocurrent density 5.16 mA/cm² at 1.23 V vs. RHE. It is due to vertical grown WO3 NRs and very low thickness of capped BiVO4 on nanorods, ALD method to produce BiVO4 nanoparticles which reduce the distance between both layers to enhance the charge transfer. Formation of p-n junction for charge separation and SPR effect of co-catalyst Co-Pi. ZnO/Ag/WO₃ gives highest degradation percentage of organic dye (CPX) which is up to 98.8 % due to formation of S-scheme heterojunction, increase of surface roughness after loading of Ag/WO₃ loading leads to more charge transfer for degradation of dye, increase in hydrophilicity of ZnO layer for surface enhancement to absorb CPX on the surface and SPR effect of Ag which increases the transfer of charges for photo-degradation. After discussion of several mechanisms, an insightful mechanism is inclined for charge transfer in ternary composite which might be helpful to further enhance the activity of metal-based composites like; metal oxide, metal sulfide, metal nitrides, metal carbides (Fig. 9). In Fig. 9, proposed scheme consists of three semiconductor catalysts listed as: semiconductor-1, semiconductor-2 and semiconductor-3. The band gap and band alignment of all semiconductors can be adjusted and band gap of semiconductor-1 may be less than or equal to 3.2 eV, semiconductor-2 may be less than or equal to 2.0 eV and semiconductor-3 may be less than or equal to 2.5 eV. After these adjustments there is a discussion of the mechanism of charge

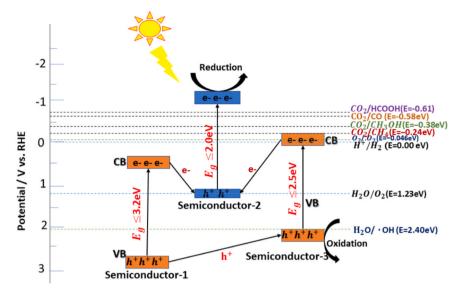


Fig. 9. Schemes for semiconductors with different band alignments for transfer of charge carriers.

Table 1
Metal oxide-metal oxide heterojunctions for Photocatalytic applications.

| Photocatalysts- Sensitizers | Synthesis Methods | Heterojunction | Activities | Reference |
|---|---|----------------------------|---|-----------|
| ΓiO ₂ -Fe ₂ O ₃ | Hydrothermal-ALD | Type-II | 3.6 mA/cm ² Photocurrent density at 1.23 V vs. RHE | [64] |
| WO ₃ -BiVO ₄ | Glancing angle deposition-Normal physical sputtering | Type-II | $5.16~\mathrm{mA/cm^2}$ Photocurrent density at $1.23~\mathrm{vs.}$ RHE | [66] |
| ΓiO ₂ -WO ₃ | Hydrothermal-Hydrothermal | Type-II | $0.216~\mathrm{mA/}cm^2$ Photocurrent density at $1.2~\mathrm{V}$ vs. RHE | [67] |
| °iO ₂ -Ag ₂ O | Hydrothermal-CBD | Type-II | $1.616~\mathrm{mA}/\mathrm{cm}^2$ Photocurrent density at $1.23~\mathrm{V}$ vs. NHE | [68] |
| °iO ₂ -Cu ₂ O | CBD-CBD | Type-II | $2.56~\text{mA}/\text{cm}^2$ Photocurrent density at $1.23~\text{V}$ vs. RHE | [69] |
| TiO ₂ NRS- TiO ₂ NBs | Hydrothermal-Hydrothermal | Type-II | $1.246~\mathrm{mA}/\mathrm{cm}^2$ Photocurrent density at $1.23~\mathrm{V}$ vs. NHE | [70] |
| CiO ₂ NWs- ZnO | Wet chemical method-Wet chemical method | Type-II | O II degradation $-53~\%$ under UV and 72 $\%$ under visible light | [71] |
| e ₂ O ₃ -ZnO | Sol gel-spin coating | Type-II | SA degradation 64 % under UV light | [72] |
| nO-ZnFe ₂ O ₃ -TiO ₂ | Hydrothermal-Hydrothermal- Hydrothermal | Dual type-II | Degradation of MB up to 96.32 % | [74] |
| inFe ₂ O ₄ -TiO ₂ | Hydrothermal-Sol gel | Type-II | Reduction of CO_2 to methanol is 693.31 µmol (g cat) ⁻¹ | [75] |
| iO ₂ -ZnO | Hydrothermal-Spin-coating | Direct Z-scheme | 2.756 mA/cm ² Photocurrent density at 1.23 V vs. RHE | |
| - | , , | | , | [82] |
| nO-Fe ₂ O ₃ | Spin coating-Sol gel | Direct Z-scheme | SMA degradation 95.2 % under visible light and DA sensing is $0.18\mu\text{M}$ | [83] |
| nO-WO ₃ | Solvothermal-Solvothermal | Direct Z-scheme | $3.38 \text{ mA}/\text{cm}^2$ photocurrent density at 1.23 V vs. RHE with 1000 rpm | [84] |
| uO-WO ₃ | Self-assemble method – self-assemble | Direct Z-scheme | Production of 1.58µmol/g/h CO from CO ₂ | [86] |
| nO-AgI-WO ₃ | Hydrothermal-Hydrothermal- Hydrothermal | Double direct Z- scheme | 85.2 % rate of MB degradation | [85] |
| u2O-TiO2 | Solvothermal-Solvothermal | Direct Z-scheme | Photoreduction of CO ₂ to CO is 2.11µmol (g cat) ⁻¹ | [87] |
| nFe ₂ O ₄ -Ag-TiO ₂ | Solvothermal-photo deposition- Hydrothermal | Solid state Z-scheme | Production of CO, CH ₄ , CH ₃ OH and C_2H_6 is 1025, 132, 30.8 and 19.1 umolg $^{-1}$ cat $^{-1}$ | [90] |
| -Fe ₂ O ₃ -Au-TiO ₂ | Hydrothermal-Pulsed laser deposition- Hydrothermal | Solid state Z-scheme | 1.05 mA/cm ² Photocurrent density at 1.23 V vs. RHE | [91] |
| iO ₂ -Cu-ZnO | Hydrothermal-ALP-Spray pyrolysis | Solid state Z-scheme | Production of H ₂ is 342.0µmol/g/h | [92] |
| g ₂ O-Ag-TiO ₂ | Stober Method-Stober Method- Hydrothermal | Solid state Z-scheme | Photocurrent production is 28.2 nA | [93] |
| g-Fe ₂ O ₃ -TiO ₂ | Condensation reflux method-Hydrothermal | Solid state Z-scheme | Highest kinetic constant value $0.027 \mathrm{min}^{-1}$ for degradation of Rh B | [94] |
| iO ₂ -Bi ₂ O ₃ | Hydrothermal-Hydrothermal | S-scheme | Photocatalytic H ₂ production 12.08µmol/g/h | [101] |
| nO-ZnMnO ₄ | Electrospinning-Electrospinning | S-scheme | $1.06 \text{ mA/}cm^2$ Photocurrent density at 1.23 V vs. RHE | [102] |
| nO-WO ₃ | Hydrothermal-Hydrothermal | S-scheme | 6788 μ mol L ⁻¹ h ⁻¹ H ₂ O ₂ production | [103] |
| nO/Ag/WO ₃ | Spray pyrolysis - Spray Pyrolysis -Spray pyrolysis | S-scheme | Degradation of CPX 98.8 % | [104] |
| ZnO-V ₂ O ₅ -WO ₃ | Electrospinning-Electrospinning- Electrospinning | Dual S-scheme | Degradation of CR, RB, MO, SO and MB is 67 %, 86.6 %, 98.0 %, 76.8 % and 99.0 % | [105] |
| Ga ₂ O ₃ -ZnO-WO ₃ | Electrospinning-Electrospinning- Electrospinning | Dual S-scheme | Degradation of Rh B | [106] |
| °iO ₂ -Bi ₂ O ₃ | Hydrothermal-Photo-deposition | S-scheme | $1.15~{ m mM~h^{-1}~H_2O_2}$ | [107] |

separation, migration and reactions on CB and VB of semiconductor catalysts. Under light illumination the electrons in the VB of all semiconductors absorb photons and get excited and migrate to their CB. The migration of charge carriers causes an interface between them and the type of interface tells the route of charge transportation. In this heterojunction the electrons from the CB of semiconductor-1 and semiconductor-3 may transfer to VB of semiconductor-2 for recombination while holes from VB of semiconductor-1 may migrate to VB of semiconductor-3. The photoexcited electrons in the CB of semiconductor-2 at higher reduction potential causes reduction and holes in the VB of semiconductor-3 causes oxidation. It can be explained by taking an example. Consider semiconductors 1, 2,3 as three layers of metal oxides (MO-1, MO-2, MO-3) and the percentage compositions of each layer could be adjusted as MO-1 is 25 %, MO-2 is 40 % and MO-3 is 35 %. As MO-1 layer has larger band gap then it can make the composite stable from photo corrosion in the presence of light and its electrons may not participate in any reaction as CB is below zero potential and recombine with holes of MO-2 layer. MO-3 layer is 35 % because its band gap is less than and equal to 2.5 eV and its CB is above zero potential and different kinds of reactions can take place here such as; CO₂ reduction, water splitting and dve degradation under sunlight. MO-2 layer may be 40 % and smaller band gap because there can be lot of reactions occurring in its CB like; CO₂ reduction to HCOOH, CO, CH₃OH, CH₄ and dye degradation and water splitting to produce hydrogen. At the end it is inferring that this scheme can be used for any kind of ternary composite by adjusting the percentage of each layer and can be used for any kind of reaction and for one reaction or more than one reaction at a time.

3. Metal oxide-metal sulfide based composites

Metal oxides are used for refining and decomposing wastes and organic substances due to their chemical, physical and optical properties [108]. When the grain size of metal oxides is decreased new possibilities are opened, especially in photocatalysis because as the size decreases, the active sites on the surface of metal increase as compared to their bulk size. Metal oxides form photocatalysts which are enriched enough to absorb light and have compatible and stable morphology, reusable and have large surface area [109]. Metal sulfide photocatalysts are cost effective and ecofriendly and can split water into oxygen and hydrogen. Metal oxides have a wide band gap due to 2p orbitals of oxygen and their localized 2p holes. In contrast, metal sulfides have open exposure of active sites, strong catalytic and photocatalytic abilities, narrow band gap, a suitable band position and utilize a wide solar spectrum. Synthesis of metal oxide and metal sulfide make them effective semiconductor photo electrocatalysts [110].

3.1. Type-II heterojunction

The H₂ evolution of ZnIn₂S₄/AgFeO₂ photoanode is 9.14 µmol/h/g (Fig. 10a-b) at 3 % content of AgFeO₂ which is approximately 30 times higher than pure ZnIn₂S₄ (0.31 mmol/gh). ZnIn₂S₄ and AgFeO₂ photocatalysts are n and p type semiconductors, respectively. The VB and CB values of AgFeO2 are 1.69 eV and -0.08 eV and VB and CB values of ZnIn₂S₄ are 1.89 eV and -0.61 eV. The Fermi-level values of ZnIn₂S₄ and AgFeO2 are approximately -0.65 and 1.25 V (vs SCE) which are calculated by Nernst equation: $E_{NHE} = E_{SCE} + 0.224$. Before contact E_f of ZnIn₂S₄ is more negative than valence band potential and E_f of AgFeO₂ is more positive than conduction band potential. After loading AgFeO₂ nanoparticles on the ZnIn₂S₄ microsphere, a p-n heterojunction is formed at their contact interface. Due to different values of Fermi-level between two components electrons will migrate from p-type to n-type semiconductors until the Fermi-levels of both components attain equilibrium. Meanwhile, the VB of AgFeO₂ increases with E_f and CB of $ZnIn_2S_4$ decreases with E_f . The internal electric field is formed from ZnIn₂S₄ towards AgFeO₂ after the contact and CB position of AgFeO₂ will be more negative than the CB position of ZnIn₂S₄. Upon light irradiation electrons and holes are generated. The electrons of both semiconductors migrate from VB to CB leaving the holes behind. Due to synergistic effects of internal force electrons can easily travel from CB of AgFeO₂ to CB of ZnIn₂S₄ and then these electrons reduce H₂O into H₂ and holes travel from VB of ZnIn₂S₄ to VB of AgFeO₂ and consumed by sacrificial agent. The mechanism in which electrons travel from CB of ptype semiconductor to n-type semiconductor and holes travel from VB of n-type semiconductor to VB of p-type semiconductor are Type-II mechanisms (Fig. 10a-b), indicating Type-II scheme mechanism [111].

Also, a three-dimensional CdIn₂S₄ (E_g=2.53 eV) deposited over TiO₂ photoanode showed the photocurrent density of 3.8 mA/cm² at 0.2 V vs. Ag/AgCl under AM1.5 solar light illumination that is three times of bare TiO2. Electrons in CB of CdIn2S4 migrate to CB of TiO2 and then to FTO and cause reduction and holes travel in opposite directions causeing oxidation and giving n-n based type-II mechanism [112]. Moreover, 2D $ZnIn_2S_4$ nanosheets (E_g =2.91 eV) and 1D TiO_2 nanorods heterojunction was developed that showed photocurrent density of 1.2 mA/cm² at G1.5AM illumination and 1.5 V vs. RHE that is 3 times higher than bare TiO₂ nanorods with onset potential reduced significantly from 0.05 V to -0.53 V. This negative shift of onset potential shows large accumulation of electrons in the heterojunction and decreased charge recombination, evidencing n-n based type-II heterojunction [113]. A type-II heterojunction of 3D rosette-rode TiO2/Bi2S3 was developed and showed photocurrent density of 3.98 mA/cm2 at 1.23 V vs. NHE using Na₂SO₃ and Na₂S as electrolyte under 100 mWcm² solar light illumination that is 10 times higher than rutile TiO₂ NRs and 5.5 times higher than RT-Bi₂S₃ photoanode synthesized via without seeding layer. As the conduction

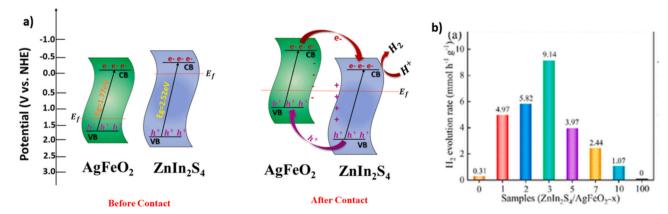


Fig. 10. a) Photocatalytic mechanism for ZnIn₂S₄/AgFeO₂ composite through p-n heterojunction under visible-light irradiation b) Photocatalytic H₂ evolution rate. Reproduced with permission [111]. Copyright 2021, American Chemical Society.

band of Bi₂S₃ is more negative then electrons would migrate from CB of Bi₂S₃ to CB of TiO₂ to FTO and cause reduction while holes travel in opposite direction and cause oxidation of sacrificial agent [114]. Also, Sb_2S_3 (E_g =1.7 eV) over TiO_2 heterojunction showed photocurrent density of 9 mA/cm² at -0.4 V vs RHE in 1 M sulfuric acid solution under 1 sun illumination. From X-ray photoelectron spectroscopy (XPS) band alignment studies and bias-dependent incident-photon conversion efficiency (IPCE) shows that Sb₂S₃ is weakly n-type, has short diffusion length and large CBO of heterojunction and can be improved by buffering with In₂S₃ by reducing CBO, higher CB position and higher onset potential which is 0.25 V. If its mechanism was studied, its electrons would travel from CB of Sb₂S₃ to CB of TiO₂ under light illumination and holes travel from VB of TiO2 to VB of Sb2S3 cause reduction and oxidation exhibiting type-II heterojunction [115]. Similarly, β-In₂S₃ is sensitized over TiO2 by spin coating and hydrothermal method at different temperatures as TiO₂/In₂S₃-(6, 8, 10, 12 and 14). TiO₂/In₂S₃-12 showed highest photocurrent density 0.1256 mA/cm² at 0 V vs. saturated calomel electrode (SCE). After migration of photoexcited electrons the Fermi-levels of both photocatalysts come in equilibrium due to interfacial contact. Electrons transfer from CB of In₂S₃ to CB of TiO₂ by passing the interface (CB of In₂O₃) to FTO substrate and holes travel in opposite directions for reduction and oxidation and form type-II mechanism [116]. Heterojunction of α-Fe₂O₃/Bi₂S₃ showed photocurrent density 2.550 mA/cm² at 1.23 V vs RHE 20 times higher than pristine α-Fe₂O₃. EIS showed that sample prepared in 6 h has lowest $R_p(180.9 \,\Omega cm^2)$, indicating enhanced photocatalytic performance under 1 sun illumination, demonstrating p-n based type-II heterojunction [117]. Also, a ternary heterostructure of 1D TiO2/CdS/ZnS was developed that showed highest photocurrent density of 5.84 mA/cm² and photovoltaic efficiency of 3.43 % due to formation of type-II heterojunction. The photoexcited electrons travel from CB of ZnS to CdS to TiO₂ for reduction and holes in their VB travel in opposite direction. The passivation of ZnS layer possess a low mismatch quantum dot (QDs) and CB is more negative inhibit electrons to enter in electrolyte and passivates dangling bond on CdS surface which reduces recombination of CB of CdS and TiO₂ [118]. Similarly, TiO₂/PbS/ZnS heterojunction was synthesized which worked in the same way, as a ternary heterojunction, as discussed above to increase photovoltaic efficiency 0.20 % [119]. As the charge transfer in type-II heterojunction takes place from CB of one semiconductor to CB of other semiconductor will reduce the spatial electrons and holes transfer due to electrostatic repulsion between electrons and holes. Similarly, the attraction between electrons and holes also hinders the electron from one semiconductor to another. It is finally summed up that it fails to separate the photogenerated electrons and holes and weakens the redox ability.

3.2. Direct Z-scheme heterojunction

A heterostructure of Bi₂S₃ nanosheets on hydrogen treated TiO₂ nanorods (NRs) was developed by facile solvothermal method. The photocurrent density of heterostructure was 2.35 mA/cm² at 1.23 V vs. RHE that is 16 times higher than bare TiO2NRs. The charge transfer mechanism was investigated via photoluminescence (PL) spectra by using terephthalic acid (TA) as a probe molecule to characterize radical OH production under illumination. In TA solution TAOH with PL emission was centered at 425 nm formed by combining OH with TA. The production of OH radical is more in heterojunction than H-TiO₂ and proposed the z-scheme mechanism in heterostructure. The photoanode is exposed under solar light irradiation, the electrons in their valence band migrate to their conduction band leaving the holes behind. As the Fermi-level of both semiconductors exhibit equilibrium the z scheme heterojunction is formed. The electrons of H-TiO2 combine with the holes in the VB of Bi₂S₃ which improves the separation and extraction of charge carriers. Meanwhile oxygen vacancies are formed in H-TiO2 due to H2 treatment reducing the charge recombination. The electrons in CB

of Bi_2S_3 take part in reduction to produce H_2 and holes in VB of H-TiO₂ cause oxidation of sulfur ion and sulfite ion to sulfate ions [120].

Another photoanode consisting of CdS over TiO2 nanosheets based heterostructure was developed by successive ionic layer adsorption and reaction (SILAR) technique produces photocatalytic H₂ of 51.4 µmol/h. The photocatalytic activity is enhanced by Z-scheme heterojunction that causes efficient charge separation and migration of charge carriers from TiO₂ nanosheets to CdS nanoparticles at their interface. It is confirmed by PL spectra by using coumarin as a probe molecule. The electrons in the CB of CdS are transferred to TiO2 and Fermi-levels come in equilibrium. During this process an internal magnetic field is produced which restrains transfer of electrons from CdS to TiO2. Therefore, electrons started migrating from CB of TiO2 to VB of CdS and electrons of CdS and holes of TiO2 cause reduction and oxidation at the respective surface active sites [121]. Also, a 2D photoanode of ZnS (E_g =3.6 eV) on ZnO (E_g =3.2 eV) was synthesized by hydrothermal method indicating the direct z-scheme heterojunction. The mechanism for 2D-ZnS@ZnO represents that the CB potential and VB potential of ZnS are -0.31 eV and 2.89 eV. The CB edge potential and VB edge potential of ZnO are 2.56 eV and -0.14 eV. As the CB of ZnO is not more negative than the reduction potential for the photocatalytic hydrogen production. Therefore, it can possibly form the Z scheme heterojunction for photocatalytic hydrogen generation. Upon solar light illumination, the electrons of ZnO and ZnS stimulated from VB to the CB leaving the holes in the VB. The photogenerated electrons are accelerated by built-in electric field in the ZnO and formation of electrostatic attraction at the interface of the heterostructure. The least effective electrons of ZnO recombine with the holes of ZnS due to electrostatic attraction between electrons and holes of ZnO and ZnS. The powerful electrons of ZnS react with H+ ions and produce hydrogen and holes are scavenged by electrolyte. The direct Z scheme nanocomposite of 2D-ZnS@ZnO produces photocatalytic hydrogen is 1552 µmol [122]. Similarly, a direct Z scheme heterojunction of WO3 and ZnS was developed for degradation of tetracycline antibiotic 48.8 % by hydrothermal method. The mechanism involves recombination of photogenerated electrons of ZnS CB and holes of WO3 VB which supports role of O₂ radicals as the potential level of electrons in the CB of WO3 is unable to reduce oxygen. Therefore, electrons and holes of higher reduction and oxidation potential are participating in degradation [123] as shown in Fig. 11. Also, a direct Z- scheme core-shell hybrid nanofiber of TiO2/NiS was synthesized by hydrothermal and electrospinning methods. The heterostructure produced 655 umol/g/h hydrogen from water not from H-containing contaminants. The scheme shows recombination of electrons of TiO2 and holes of NiS while electrons of NiS shows reduction of water and holes of TiO2 shows oxidation of sacrificial agent of methanol [124]. Furthermore, a Z-scheme heterojunction of CdS/BiVO₄ composite with 15-20 nm thickness produces more CH₄ and CO than the composite with 55-75 nm thickness of BiVO₄ nanosheets. The difference in their activities is due to more visible light irradiation, small electron diffusion length, less charge recombination, more charge separation and formation of Z scheme heterojunction. The production of CH₄ and CO by nanosheet of BiVO₄ is 8.73 and 1.95 μ mol g⁻¹ after 5 h irradiation [125]. The direct Z scheme heterojunction has many advantages due to formation of heterojunction without any mediator. Firstly, the temporal stability of this heterojunction is considerably prolonged because of resistance to photocorrosion which usually occurs due to the presence of solid mediators. Secondly, the backward reactions in the photocatalysts are weakened. Thirdly, the shielding effect of solid mediators between the charge carriers between both semiconductor photocatalysts reduces. Finally, the binary structure is favorable over the ternary structure which is comparable to type-II heterojunction due to facile and cost-effective fabrication.

3.3. Solid-state Z-scheme heterojunction

Xu et. al., prepared a ternary composite of CdS/Ag/TiO2 NTs by

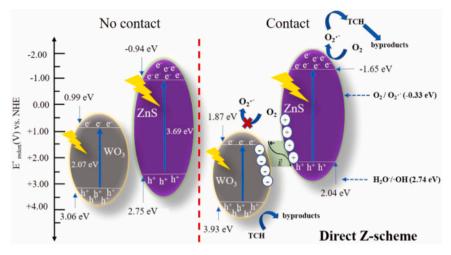


Fig. 11. Schematic representation of charge transfer for ZnS /WO₃ nanocomposite for Tetracycline Degradation. Reproduced with permission [123]. Copyright 2021, Elsevier.

hydrothermal, photoreduction and SILAR method to increase photocatalytic activities (Fig. 12a-c). The composite showed photodegradation of RhB 82.24 %/3 h and MB 100 %/2 h (Fig. 12c) and rate of H₂ production is 806.33 μ mol/h/cm² in one hour. The increase in photocatalytic activities is due to the synergetic effect between TiO₂, Ag and CdS showing an indirect Z scheme. The band gap of TiO₂ NTs is 3.15 eV with CB and VB values are -0.26 eV and 2.89 eV and the band gap of CdS is 2.16 eV with CB and VB values are -0.40 eV and 1.76 eV. Under light illumination, photoexcited electrons in CB of CdS and holes in the VB of TiO₂ recombine on Ag surface. Meanwhile electrons in CB of TiO₂ and holes in the VB of CdS cause formation of O_2^- and OH radicals further involved in photodegradation and H₂ production (Fig. 12a) [126].

Noticeably, an indirect Z-scheme heterojunction of TiO_2 -Au-CdS showed photocurrent density of 6.99 mA/ cm^2 at 1.23 V vs. RHE that is 1.89 times higher than TiO_2 -CdS and H_2 production is 46.64 μ mol/ cm^2 /h that is 84.50 times higher than pristine TiO_2 due to Au bridge. Under light illumination, photoelectrons migrated to their CB. The electrons of TiO_2 transferred to Au nanoparticles through the Schottky barrier and holes of CdS to Au and recombination occurs. The electrons of CdS migrated to CB of TiO_2 causes reduction of water while holes of

TiO2 transfer to VB of CdS and quenched by sulfide ions of electrolyte [127]. Also, 3D TiO₂-Au-CdS produced 1.81 mmol/h/g by above mentioned mechanism [128]. Similarly, a solid-state Z-scheme of ZnO-Au@CdS was prepared which has 79 and 28 times higher photocatalytic activity than ZnO and ZnO-Au [129]. Also, a 3D heterostructure of CdS-Au-ZnO was developed by hydrothermal, sonication and seeding which produced photocatalytic hydrogen of 102.9 µmol/h. Under light illumination, electrons of CdS and ZnO got excited and migrated to their CB. Au acts as electron mediator and produces surface plasmon effect resonance (SPR) effect. The electrons after band alignment transfer from CB of ZnO to Au and holes of CdS to Au cause recombination and increase the flow of electrons to CB of CdS and increase the reduction of water with higher reduction potential. Meanwhile, holes in VB of ZnO cause oxidation of sacrificial agents in the electrolyte [130]. The discussion of solid-state Z scheme heterojunction presented the key factors for enhancing the catalytic activity of the photoinduced interparticle electron and hole transfer. (a) The rate determining step is the charge transfer from one semiconductor to another via solid mediator. (b) The photoactivity of the photocatalysts is enhanced by the balance of conductivity and hydrophobicity of the mediator. (c) The control of annealing time and temperature reduces the

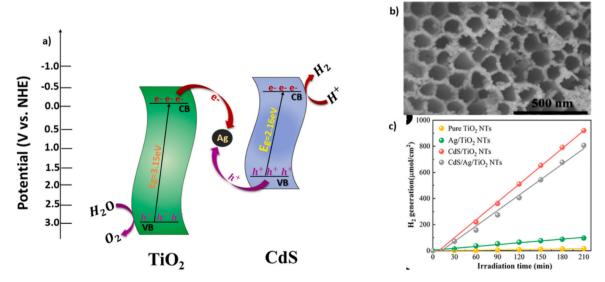


Fig. 12. a) Schematic illustration of charge transfer of $TiO_2/Ag/CdS$ heterostructure, b) SEM of $TiO_2/Ag/CdS$ heterostructure and c) Dye absorbance after photocatalyst adsorption. Reproduced with permission [126]. Copyright 2022, Elsevier.

resistance of charge transfer between the mediator and the semiconductor photocatalyst as well as the Schottky barrier between the metal and semiconductor is also minimized.

3.4. S-scheme heterojunction

For the photocatalytic reaction S scheme heterojunction plays an important role to enhance the photoactivity. There are some strategies to develop the S scheme heterojunction photocatalysts with stronger redox ability such as; Cocatalyst loading, morphology control, interface optimization and reaction activation barrier for charge carrier transfer. For example; Park et. al., synthesized a core-shell CoS@TiO2 heterostructure by positively charged cobalt sulfide micro sheet particles and negatively charged TiO2 nanoparticles using hydrothermal method (Fig. 13a-c). The setup for H₂ production and determination was developed (Fig. 13a). The CoS@TiO2 photoanode has strong ability to absorb visible light and produced 1945 µmol/g for 10 h (Fig. 13b) which is 114.4 and 13.2 times higher than p-CoS (E=1.57 eV) and n-TiO2. Generally, as the intensity of PL spectra decreases the recombination of electrons and holes decreases and photocatalytic performances increase. In CoS@TiO2 heterojunction very low intensity of PL spectra is obtained at 825 nm so the electrons in CoS particles did not relax through interface transitions after excitation from S 2p to Co 3d and remained in the core shell. Therefore, electrons did not flow from CoS to TiO2 nanoparticles and followed the S-scheme mechanism (Fig. 13c). This mechanism consists of reduction photocatalyst (RP) and oxidation photocatalyst (OP) with staggered band gap energies equal to energy of z-scheme. But in s-scheme redox potential is way stronger than z-scheme due to recombination of unnecessary electron-hole pairs. According to spin-coating ESR trapping mechanism, under solar light OH radicals gather in VB of TiO₂ and O₂ radicals gather in CB of CoS and show an sscheme mechanism instead of type-II. In this scheme electrons get excited under light illumination in both photocatalysts and migrate to CB. The electrons travel from CB of CoS to VB of TiO2 while electrons of TiO₂ cause reduction of water and holes of CoS cause oxidation of lactic acid [131].

Noticeably, a ternary p-n-p heterojunction- based S-scheme containing CuO/CdS/CoWO₄ was developed by hydrothermal and microwave hydrothermal methods. The photoanode showed higher values of catalytic hydrogen production which is 457.9 μ molg⁻¹h⁻¹ that is 3.14, 11.99, 40.88 and 102.9 times higher than CuO/CdS, CdS, CuO and CoWO₄, respectively. The band gap of the photoanode is 2.40 eV. This

heterojunction shows stability even after five cycles during production of H2 and can be reused. After in contact, an internal electric field is produced causing adjustment of their Fermi-levels and electrons are migrated from CB of CuO and CB of CoWO₄ to VB of CdS. The electrons of CdS cause reduction and holes of CuO and CoWO4 cause oxidation [132]. Chen et. al., developed an S-scheme based CuO/CdS QDs for degradation of chlortetracycline up to 86.8 % and have current density 3.42 A/m^2 . The PL spectra show excitation wavelength at 350 nm to avoid charge carrier recombination. Electrons of CuO and holes of CdS combine and electrons of CdS and holes of CuO cause reduction and oxidation [133]. Also, S-scheme heterojunction in TiO2/CdS nanocomposite produces photocatalytic hydrogen of 2.32 mmol/h/g which is 35 times higher than the pristine TiO2. The electrons of TiO2 are useless and recombine with holes of CdS. Meanwhile the useful electrons of CdS cause reduction of water and holes are quenched by methanol [134]. Similarly, a S-scheme heterojunction of CdS/TiO₂ hollow microsphere was prepared by hydrothermal method for reduction of CO_2 to CH₄. The photocatalytic reduction produces 27.85 $\mu \text{mol g}^{-1}\ h^{-1}$ which is 145.6 and 3.8 times higher than pristine CdS and TiO2 due to multi scattering of visible light, photocatalytic reactions take place on both outside and inside surface of shell and intimate contact between both semiconductors making S scheme by in-built electric field causing reaction at higher redox potential [135].

Among the discussed examples of metal oxide and metal sulfide composites, TiO₂/Sb₂S₃ has highest photocurrent density 9.0 mA/cm² at 1.23 V vs. RHE due to placing Pt co-catalyst and buffering layer In₂S₃ in between TiO₂ and Sb₂S₃. It is prepared by atomic layer deposition and chemical bath deposition having charge transfer mechanism is of type-II heterojunction. But TiO₂-Au-CdS has 6.99 mA/cm² photocurrent density at 1.23 V vs. RHE under 1 sun illumination. It has Au metal as a bridge due to very low concentration producing Schottky barrier and increases the flow of electrons to CB of TiO2 for H2 production and reduces the recombination of charges creating indirect Z-scheme heterojunction. TiO2 NTs-Ag-CdS composite prepared by hydrothermal, electrospinning and SILAR methods gives highest value of degradation of organic dyes (MB and Rh B) 100 %, 82 % and produce H₂ 806.33 µmol/g/h due least electron recombination and SPR effect of Au. At the end there are few points which are necessary to choose the photocatalysts for best heterojunction to enhance the activity of that composite. These are: appropriate matching of CB and VB potential, stability of the composite in the electrolyte, highly stable in the light, effective charge separation, beneficial charge transfer which leads to water

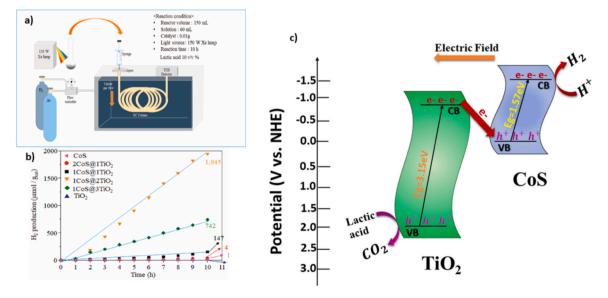


Fig. 13. a) Schematic diagram for CoS@TiO₂ core-shell heterojunction b) H₂ production from water splitting in the presence of lactic acid. Reproduced with permission [131]. Copyright 2021, Elsevier.

splitting and reduction of CO₂ at better redox potentials and degradation of dyes to less harmful material. The best heterojunction of metal oxide and metal sulfide photocatalysts can be formed by selection of metal oxide and metal sulfide which overcome the weakness of each other. For example, metal oxides possess poor separation efficiency, low mobility, slow surface gas evolution efficiency. Therefore, metal sulfide should be selected which have narrow band gap, high light absorption efficiency to facilitate charge separation, transfer and subsequently, promote respective product formation and desorption kinetics from the surface active sites. By keeping all these aspects, an accountable scheme containing ternary nanocomposite is introduced as shown in Fig. 14 which could be helpful to enhance the activity of any heterojunctions based upon metal oxide-metal sulfide heterojunctions schemes for different kind of reactions such as CO2 reduction, water reduction, dye degradation and any kind of oxidation reactions. In this scheme of Fig. 14, there are three layers comprised as: semiconductor-1, semiconductor-2 and semiconductor-3 with band gap of first layer may be greater than or equal to 2.0 eV, second layer may have band gap greater than or equal to zero and less than or equal to 2 eV and third layer may have band gap equal to or greater than 2.5 eV. The semiconductor-1 catalyst might be CB lower than zero potential so its electrons cannot be able to do effective reduction and semiconductor-2 has CB band higher than zero potential but VB is higher than oxidation potential required for any kind of oxidation reaction. Meanwhile semiconductor-3 can have CB at higher reduction and higher oxidation potential and higher stability but wide band gap which may not be feasible for any reaction to occur. After knowing the pros and cons of every layer a heterojunction can be formed that may have maximum electrons to participate in the reduction reaction and maximum holes for oxidation reactions. Under light illumination the electrons absorb visible light and migrate from VB to CB. Due to migration of charge carriers an internal field is produced which creates an interface between all three-semiconductor catalysts. According to type of interface between semiconductor-1 and semiconductor-2 useless electrons of first layer can recombine with holes of second layer. Meanwhile the electrons from CB of third layer may transfer to CB of second layer due to different type of interface formation and these electrons can cause reduction reaction. The holes of semiconductor-2 might be used up for recombination; the holes from VB of semiconductor-1 may migrate to VB of semiconductor-3 because holes always travel from more positive VB to less positive VB and cause oxidation reactions. Let's explain this scheme by taking an example of ternary nanocomposite consisting of metal oxide and metal sulfide layers and can be represented as: semiconductor-1 and semiconductor-3

can be MO-1 and MO-3 and semiconductor-2 is considered as MS-2 layers. The percentage composition of every layer could be adjusted according to requirements for the reaction to proceed with high photocatalytic activity. Here, MO-1 layer can be 20 % because no reaction can take place on this layer but its band gap is small so it might help in absorption of maximum visible light. MS-2 layer might be 50 % because maximum reactions like water splitting, CO2 reduction to aldehyde, methane, CO, alcohol and dye degradation could take place. Meanwhile the composition percentage of MO-3 layer may be 30 % because it has wide a band gap which can be helpful to provide stability to heterostructure and also transfer electrons to CB of MS-2 which cause reduction reaction and can take holes from MO-1 to its VB to do oxidation reaction. Lastly, this scheme can be used for any kind of ternary composite like metal sulfides, metal oxides, metal carbides, metal nitrides and many more and can also be utilized for more than two reactions at a time.

4. Metal sulfide-metal sulfide composites

Metal sulfides are introduced as a good candidate for visible light driven reactions such as photoelectrochemical water splitting to produce $\rm H_2$ and $\rm CO_2$ reduction. Remarkably, metal sulfides have better electron/hole pair separation efficiency than metal oxides, therefore, they are used as better visible light driven photocatalysts [138]. The valence band of metal sulfides are occupied by S-3p orbitals, and their position is higher than O-3p orbitals, which gives rise to form less positive VB and higher mobility of electrons and holes for acceleration of charge transfer in them. Metal sulfides have unique features like suitable band gap, tunable surface electronic configuration, and abundant active sites for water splitting applications to produce hydrogen [139]. Metal sulfides have a problem of photo corrosion which can be solved by forming composites with other somewhat stable metal sulfides.

4.1. Type-II heterojunction

Type-II of MnIn $_2$ S $_4$ /Cu $_7$ S $_7$ heterojunction has improved hydrogen production activity which is 13.81 µmol/h (Fig. 15a-b) that is 18 times higher than pristine MnIn $_2$ S $_4$. It is due to p-n heterojunction which exhibits inhibition of charge recombination and higher charge carrier separation (Fig. 15a). In this heterojunction, CB values of MnIn $_2$ S $_4$ and Cu $_7$ S $_4$ are -0.61 V and -0.99 V and Fermi-level of MnIn $_2$ S $_4$ is below its CB and Fermi-level of Cu $_7$ S $_4$ is above its VB. When the light falls on the composite the electrons in the valence band of both semiconductors get

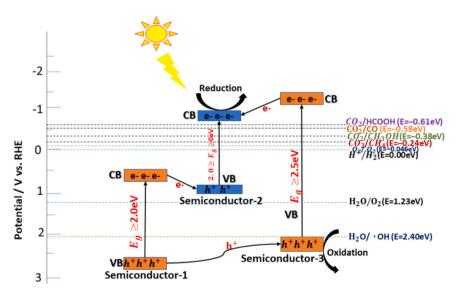


Fig. 14. Scheme for semiconductors with different band alignments for transfer of charger carriers.

 Table 2

 Metal oxide-metal sulfide-based heterojunctions for Photocatalytic applications:.

| Photocatalysts-Sensitizers | Synthesis Methods | Heterojunction | Activities | References |
|---|--|--------------------------|---|------------|
| AgFeO ₂ -ZnIn ₂ S ₄ | Coprecipitation-Solvothermal | Type-II | $0.006 \; (mA/cm^2)$ Photocurrent Density at $1.23 \; V$ vs. RHE | [111] |
| TiO ₂ NRs-CdIn ₂ S ₄ | Hydrothermal-Hydrothermal | Type-II | $3.8 \ (mA/cm^2)$ Photocurrent Density at $1.23 \ V$ vs. RHE | [112] |
| ${ m TiO_2~NRs\text{-}ZnIn_2S_4}$ | Hydrothermal-Hydrothermal | Type-II | $1.2 \; (mA/cm^2)$ Photocurrent Density at $1.5 \; V$ vs. RHE | [113] |
| 3D rosette $\rm TiO_2$ NRs-Bi $_2\!S_3$ | Hydrothermal-SILAR | Type-II | 3.98(mA/cm ²) Photocurrent Density at 1.23 V vs. RHE | [114] |
| TiO ₂ -Sb ₂ S ₃ | ALD-CBD | Type-II | 9.0 (mA/cm²) Photocurrent Density at 1.23 V vs. RHE | [115] |
| ${ m TiO_2}	ext{-}{ m In_2}{ m S_3}$ | Hydrothermal-Spin Coating | Type-II | 0.1256 (mA/cm²) Photocurrent Density at 1.23 V vs. RHE | [116] |
| $\alpha\text{-Fe}_2\text{O}_3\text{-Bi}_2\text{S}_3$ | Hydrothermal-SILAR & Solvothermal | Type-II | 2.550 (mA/cm²) Photocurrent Density at 1.23 V vs. RHE | [117] |
| TiO ₂ -CdS-ZnS | Hydrothermal-SILAR-SILAR | Type-II | 5.84 (mA/cm²) Photocurrent Density at -1.23 V vs. RHE and photovoltaic efficiency 3.43 % | [118] |
| TiO2-PbS-ZnS | Hydrothermal-SILAR-SILAR | Type-II | Photovoltaic efficiency 0.20 % | [119] |
| H-TiO $_2$ NRs-Bi $_2$ S $_3$ | Hydrothermal-Solvothermal | Direct Z-scheme | 2.35 (mA/cm ²) Photocurrent Density at 1.23 V vs. RHE | [120] |
| TiO ₂ nanosheets-CdS nanoparticles | SILAR-SILAR | Direct Z-scheme | 0.15 (mA/cm²) Photocurrent Density Vs. RHE | [121] |
| ZnO-ZnS | Hydrothermal-Hydrothermal | Direct Z-scheme | $0.72~(\text{mA/cm}^2)$ Photocurrent Density and 1552 $\mu\text{mol}~\text{H}_2$ | [122] |
| WO ₃ -ZnS | Hydrothermal-Hydrothermal | Direct Z-scheme | Degradation of Tetracycline antibiotic is 48.8 % | [123] |
| TiO2-NiS | Hydrothermal-Spin Coating | Direct Z-scheme | Production of H ₂ is 655μmol/g/h | [124] |
| BiVO ₄ -CdS | Hydrothermal-CBD | Direct Z-scheme | Production of CH_4 and CO is 8.93 and 1.95 μ mol g ⁻¹ by reduction of CO_2 | [125] |
| Cu ₃ BiS ₃ -MoS ₂ | Hydrothermal | Direct Z-scheme | Production of H ₂ O ₂ 1457 µM h ⁻¹ | [136] |
| TiO ₂ -Au-CdS | Hydrothermal-Electrodeposition-SILAR | Solid-state Z- scheme | 6.99 (mA/cm²) photocurrent density at 1.23 V vs. RHE | [127] |
| ${ m TiO_2}$ NTs-Ag-CdS | Hydrothermal-Electrospinning-SILAR | Solid-state Z- scheme | Degradation of Rh B and MB is 82.24% and 100% . H ₂ production is 806.33μ mol/g/h | [126] |
| CdS-Au-ZnO | Hydrothermal-Sonication-Spin coating | Solid-state Z- scheme | Photocatalytic production of H ₂ is 102.9 µmol/h | [130] |
| TiO ₂ -CoS | Hydrothermal-Hydrothermal | S-scheme | $0.012~(mA/cm^2)$ Photocurrent Density at $1.23~\mbox{V}$ vs. NHE | [131] |
| CuO-CdS-CoWO ₄ | Hydrothermal-Microwave hydrothermal -Microwave hydrothermal | Double S-scheme | Photocatalytic production of $\rm H_2$ is 457.9 $\mu mol/h/g$ | [132] |
| CuO-CdS | SILAR-Hydrothermal | S-scheme | Degradation of chlortetracycline is 86.6 % | [133] |
| TiO ₂ -CdS | Electrospinning-Electrospinning | S-scheme | Photocatalytic production of H ₂ is 2320µmol/g/h | [134] |
| CdS-TiO ₂ | Hydrothermal-Hydrothermal | S-scheme | Photocatalytic reduction of CO_2 to CH_4 is 27.85 μ mol g ⁻¹ h ⁻¹ | [135] |
| SnNb ₂ O ₆ /CdS | In-situ microwave solvothermal method | S-scheme | Photocatalytic production of H ₂ O ₂ is 7808 μmol g ⁻¹ h ⁻¹ | [137] |

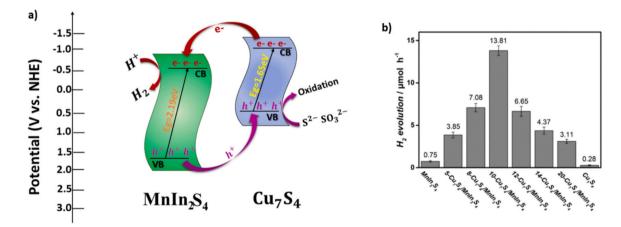


Fig. 15. a) Schematic illustration of the possible mechanism for the photocatalytic H_2 production of $Cu_7S_4/MnInS_4$ b) Hydrogen production of $Cu_7S_4/MnIn_2S_4$ heterostructure. Reproduced with permission [140]. Copyright 2021, Elsevier.

excited and migrate to their conduction bands leaving holes behind. Due to light irradiation and charge carriers' interface is formed between both semiconductors and Fermi-levels of both semiconductors come in equilibrium due to internal electric field. Then, the electrons would migrate from CB of Cu_7S_4 to CB of MnIn_2S_4 and holes travel in opposite directions in their VB. It leads to separation of electron-hole pairs and inhibits the recombination of charge carriers. In this heterojunction, MnIn_2S_4 acts as n-type semiconductor and Cu_7S_4 is p-type

semiconductor and electrons travel from p-type to n-type as a result p-n heterojunction (Fig. 15a) is formed. As electrons migrate from CB of Cu_7S_4 to CB of MnIn_2S_4 and holes in opposite directions, indicating Type-II mechanism [140].

Similarly, Bi₂S₃/CdS heterostructure was developed by facile and one-step sono-chemical methods. The photocatalytic hydrogen produced by composite (CdS/Bi₂S₃, x=0.15) is 5500 μ mol/g/h which is much higher than bare CdS photocatalyst (40 μ mol/g/h). The

enhancement in production of photocatalytic hydrogen is because of adjustment of bands for higher charge transfer and lower charge recombination. The charge transfer type-II mechanism is investigated by PL spectra as higher the PL intensity more the effective charge carriers participate in recombination while lower the PL intensity more the effective charge separation in the composite which increase the photocatalytic activities. Photoexcited electrons migrated from CB of CdS to Bi₂S₃ and holes in opposite direction and cause reduction and oxidation [141]. Also, dense array of CdS-ZnS core-shell nanorod film was established by aerosol assisted chemical vapor deposition (AACVD) method. The formation of ZnS nanocrystal on CdS nanosheets restrain photo-corrosion, enhance photoelectrochemical activities such as; increased charge separation and transportation efficiencies. The photocurrent density of heterostructure is 7.8 mA/cm² and IPCE value is above 35 % under AM1.5 G one sun illumination. The enhancement in photocurrent density and IPCE exhibited a spatial charge transfer mechanism in the CdS/ZnS nanostructure. Under light illumination, both photogenerated electrons and holes of CdS are difficult to transfer from CdS to ZnS. According to PEC performances, there are other paths for transfer of holes from valence band of CdS band gap=2.4 eV) to VB of ZnS (band gap=3.6 eV). There are different intrinsic defects like sulfur vacancies (V_s) , zinc vacancies (V_{Zn}) and interstitial sulfur (I_s) in ZnS. These acceptor states are higher than VB of ZnS and help to transfer holes from VB of CdS to VB of ZnS. The enhancement in the photocurrent density is due to migration of holes from CdS to ZnS by passing from these acceptor sites. Under light illumination, electrons get excited in VB of both semiconductors and migrate from VB to CB. Finally, electrons reach the Pt electrode by passing from CB of ZnS to CB of CdS and cause reduction of water. While holes transfer in opposite directions and exhibit quasi type-II (Fig. 16a) heterojunction [142]. While CdS-ZnS core-shell heterostructure was developed that has produced 830.95 µmol/g/h (Fig. 16b) photocatalytic hydrogen by forming quasi type-II heterojunction [143]. Also, hierarchical In₂S₃-CdIn₂S₄ nanostructured nanotubes prepared by cation exchange reaction and hydrothermal cation exchange reaction with 5 minutes and 10 minutes reaction time to adjust the morphology of final product and form different composites as In₂S₃-CdIn₂S₄-5 and In₂S₃-CdIn₂S₄-10. The In₂S₃-CdIn₂S₄-10 showed highest production of CO from CO_2 is 825 μ mol h^{-1} g^{-1} . It is due to higher separation of charge carriers, higher values of transfer kinetics of photoexcited charge carriers and these factors are attributed to unique composition and hierarchical structure of this nanotube [144]. The type-II heterojunction in the metal sulfide-metal sulfide based composites offers the enhanced photocatalytic activity due to enhanced charge carrier separation and broad visible light absorption spectra but it has some challenges which are complex synthesis process, internal defects at the interface of the semiconductors, high cost, scalability and stability which make them less effective for the photocatalytic application.

4.2. Direct Z-scheme heterojunction

Direct Z-scheme based heterojunction of CdS@ZnIn₂S₄ hollow cubes photoanode was prepared by low-temperature solvothermal method. The photocatalytic hydrogen production of heterostructure is 540.3 μmol/gh which is three times higher than ZnIn₂S₄ nanosheets (0.2μmol/ gh). According to Mott-Schottky plot, the band gap energy value of ntype $ZnIn_2S_4$ is 2.53 eV with CB and VB values are -0.57 V and 1.96 V. The band gap energy value of n-type CdS is 2.21 eV with CB and VB values are -0.90 V and 1.31 V. These band alignments of CdS and ZnIn₂S₄ results in increasing the possibilities of Z-scheme mechanism based photoexcited charge transportation. DFT calculations (Fig. 17a) show that band bending CdS-ZnIn₂S₄ interface is formed as the work function of CdS (103) was estimated 4.92 eV and 4.21 eV smaller than ZnIn₂S₄ (104) surface at 5.20 eV. EPR spectrum indicated successful detection of OH species further authenticated the Z scheme formation. Surface photovoltage mapping image (SPV) shows that composite has more positive signals than single composite and composite induced vectorial charge transfer from ZnIn₂S₄ to CdS and Z scheme pathway was depicted. Therefore, electrons are migrated from CdS surface having higher Fermi-level to ZnIn₂S₄ surface having lower Fermi-level to equilibrate Fermi-levels of both semiconductors. After Fermi-level equilibrium there is the appearance of electron layer depletion (Fig. 17b) in CdS and charge density difference in ZnIn₂S₄ producing internal electric field. It may allow recombination of electrons of ZnIn₂S₄ and holes of CdS following the Z-scheme mechanism (Fig. 17c). The electrons of CdS and holes of ZnIn₂S₄ cause reduction and oxidation of water to produce hydrogen and H_2O_2 [145].

Direct Z-scheme flower-like Bi₂S₃/SnIn₄S₈ heterojunction was synthesized for degradation of Rhodamine B which is 99.87 %. Schottky barrier is formed by combination of electrons of Bi2S3 and holes of $SnIn_4S_8$ ($E_g = 1.77-2.35$ eV), while electrons of $SnIn_4S_8$ cause degradation [146]. The hollow MoSe₂@Bi₂S₃/CdS core-shell structure was established and demonstrated dual Z-scheme heterojunction which increases the rate of quantum conversion efficiency, interface area and active sites. The ternary structure showed excellent photocatalytic activities like H₂ production 11.84 mmol/g/h, removal of Cr (VI) 98.7 % and 2,4,6-trichlorophenol (TCP) 99.2 %. Electrons of Bi₂S₃ and CdS recombine with holes of MoSe2 while electrons of MoSe2 cause reduction of water, Cr(IV) and O2 [147]. It is concluded that the synthesis methods play an important role to synthesize spatial type of heterojunction. Therefore, to synthesize the direct Z scheme heterojunction can be the deposition-precipitation methods, hydrothermal and solvothermal methods. Similarly, the best characterization techniques can be the DFT calculations, EPR analysis, SPVM and in-situ XPS.

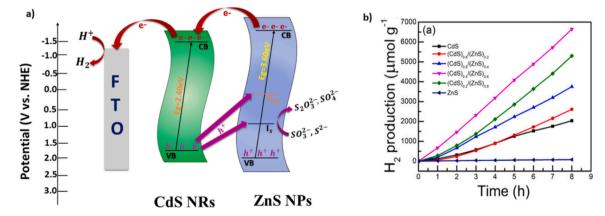


Fig. 16. a) Schematic representation of charge generation and transfer in CdS/ZnS heterojunction b) Photocatalytic H₂ production in CdS-ZnS composite with different concentrations. Reproduced with permission [143]. Copyright 2019, American Chemical Society.

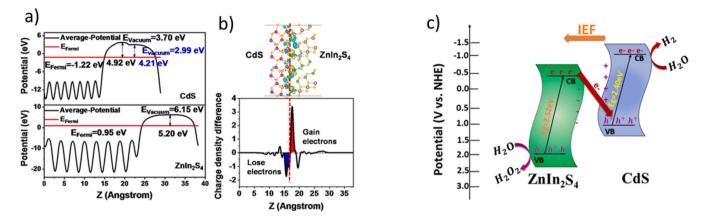


Fig. 17. a) Electrostatic Potential for CdS (103) surface and ZnIn₂S₄ (104) surface b) Simulated charge distribution at interface to get Fermi-level at equilibrium c) Charge transfer mechanism in Z-scheme heterojunction. Reproduced with permission [145]. Copyright 2021, Elsevier.

4.3. Solid-state Z-scheme heterojunction

A solid-state Z-scheme heterojunction was demonstrated by using ternary CdS/MoS₂ QDS/ZnIn₂S₄ heterojunction, where MoS₂ QDs acts as electron mediator. The ternary photocatalyst produces hydrogen of $2107.5\,\mu mol/g/h$ which is 26 and 62 times higher than CdS NRs and ZIS nanosheets, respectively. The increase in photocatalytic activity is due to the formation of z-scheme (Fig. 18) by insertion of QDs in between CdS and ZIS. The electrons on photoexcitation would travel from CB of CdS to MoS₂ ODs to VB of ZIS and then get excited and reach CB of ZIS where reduction occurs. In the same way, holes in VB of CdS cause oxidation of lactic acid and EIS of hybrids also show lower recombination than their bare forms [148]. Similarly, a ternary structure of ZnS/rGO/Bi₂S₃ showed switching of heterojunction from type-II to solid-state Z-scheme due to introduction of rGO as an electrons mediator. It converts 18.4 % solar-to-hydrogen conversion efficiency which is 2523.4 µmol/g/h and showed the highest photocurrent density of 38 mA/cm². The RGO plays an important role in enhancing the production of hydrogen due to large surface area, good conductivity, tunable band gap and hydrophobicity due to C-C bonds [149]. Furthermore, a Z-scheme heterostructure with Cd as metal bridge between Co_9S_8 ($E_g = 1.23$ eV) and CdS was also demonstrated to enhance the photocatalytic hydrogen evolution to 10.42 µmol/h which is 5.7 times higher than for pristine Cd/CdS [150].

4.4. S-scheme heterojunction

Goh et. al., enhanced photostability and photocatalytic activities of petal-shaped CdS by forming heterojunction with FeS_2 nanoparticles. The heterostructure is prepared by thermal treatment methods at different temperatures with photocatalytic hydrogen 107.56 mL/g. For

estimation of charge transfer mechanism in CdS/FeS2 heterojunction interface DMPO was used as a trapping agent to detect \bullet OH and \bullet O₂ and spin trapping analysis was performed. Even after 30 minutes of simulated sun irradiation (Fig. 19a), the DMPO-O2 signal strength in the FeS₂ particles was low. Yet, as it was a little stronger than the DMPO-•OH signal strength, it was determined that the FeS₂ particles were the source of the •O₂ radicals. Yet, the DMPO-•O₂ signal in the CdS particles had a very strong intensity that was comparable to the DMPO-OH signal. We concluded that the •OH radical was produced in the VB of CdS and the •O₂ radical was produced in the CB of FeS₂ even though the magnitudes of the two signals in FeS2 were not equal. Moreover, the junction of CdS and FeS₂ resulted in a considerable rise in the DMPO-•O₂ signal, demonstrating the synergy of the two particles. Yet, comparable to the DMPO-OH signal, the CdS/FeS2 junction catalyst's DMPO-O2 signal dramatically increased over time. As a result, it can be inferred that during the photocatalytic •O₂ radical process, the electrons generated by CdS in the CdS/FeS2 junction particles moved to FeS2 and accumulated more in the CB of FeS2. Hence, it is expected that more •OH radicals were produced in the VB of CdS during the photoreaction in the CdS/FeS₂ junction particles and more •O₂ radicals accumulated in the CB of FeS₂.Here, S-scheme (Fig. 19b) is followed due to build in electric field by reducing transport distance charge carriers at interface between two charge carriers. The built-in electric field removes useless holes and electrons in VB and CB of heterostructure and increases the separation of useful electrons and holes to produce hydrogen [151]. Also, S-scheme heterostructure was constructed to have core-shell FeS2@ZnIn2S4 with Pt as cocatalyst by quenching the useless electrons from CB of ZnIn₂S₄ and using electrons of FeS2 for hydrogen production. The composite produces H_2 of $10,100\mu mol/g/h$ which is 47.9 times higher than ZIS and 53.7 times higher than FeS2 [152]. Liu et. al., prepared ZnS/ZIS photocatalyst produces hydrogen of 2912.3µmol/g/h which is 9.0 and 33.6

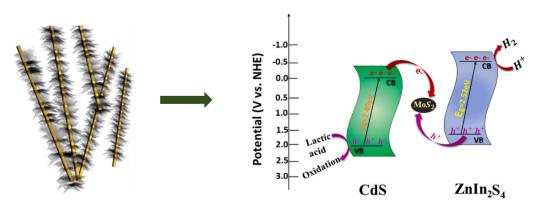


Fig. 18. Schematic representation of charge transfer in CdS/MoS₂ QDs/ZnIn₂S₄ Heterojunction. Reproduced with permission [148]. Copyright 2019, Elsevier.

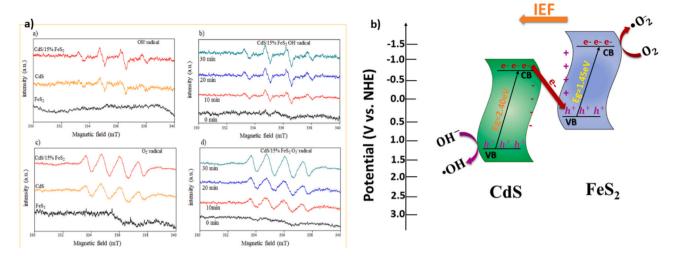


Fig. 19. a) DMPO- \bullet O₂ signals for CdS/15 % FeS₂ under light irradiation b) Charge transfer mechanism on CdS/15 % FeS₂ heterojunction. Reproduced with permission [151]. Copyright 2022, Elsevier.

times higher than ZIS and ZnS due to the S-scheme heterojunction formation [153]. Hollow nanostructure of CuS@ZIS was developed and produces enhanced photocatalytic hydrogen of 4653.43µmol/g/h and shows S-scheme heterojunction by energy band structure analysis to increase charge carrier separation [154]. A ternary composite containing CdS nanoparticles and wrapping around RGO sheets onto the surface of Bi₂S₃ as template was synthesized and produced $\rm H_2O_2$ 212.82 µmol $\rm L^{-1}$ [155].

From the above discussed examples of all type of heterojunctions of metal sulfide - metal sulfide composite of MoSe₂-Bi₂S₃-CdS is prepared by solvothermal, and hydrothermal method that produces the highest amount of hydrogen 11840µmol/g/h. The enhancement in photocatalytic activity is due to formation of core-shell structure having huge active sites for excellent light absorption. Bi2S3 and CdS with MoS2 form dual direct Z-scheme heterojunction and reduce charge recombination by forming multi-channel charge transfer. After the study of metal sulfide and metal sulfide-contained heterostructures it is noted that there are some metal sulfides which may have problems with photo corrosion, poor electrical properties, and poor charge separation. These problems are solved by formation of heterojunction with those metal sulfides and metal oxides which have narrow band gaps are photochemically stable, show great electrical and photocatalytic properties and better charge separation and charge transportation which leads to photocatalysis at lower input energy. To enhance the activity of the heterostructure there is necessary role of selection of type of photocatalyst and their adjustment in such a way that their CB and VB potentials and Fermi-levels matches mutually which further leads to stability to light illumination, charge migration, separation and transportation. According to these factors a scheme is anticipated having three different kinds of layers which might be named as: semiconductor-1, semiconductor-2 and semiconductor-3 with different band alignments to increase the activity to ternary nanocomposite. The band gap of semiconductor-1 may be less than or equal to 3.2 eV, semiconductor-2 may be less than or equal to 2.0 eV and semiconductor-3 may be less than or equal to 2.5 eV. As the CB of all semiconductor photocatalysts might be above zero potential so electrons in their CB can be useful for the reduction reaction. Therefore, such a type of interface can be constructed among all of them so that electrons of all semiconductors can be utilized for the reaction to enhance the activity of the photocatalyst. Under solar light irradiation the charge carriers absorb light and electrons migrate from their VB to CB leaving the holes behind. Due to transportation of charge carriers' interface is formed among all layers. On the basis of interface formation and band positions electrons from CB of semiconductor-1 and semiconductor-3 travel to CB of semiconductor-2 and reduction takes place. Meanwhile, holes from VB of semiconductor-1 transfer to semiconductor-2 and then subsequently to semiconductor-3, where the oxidation reaction takes place. This heterojunction can be illustrated by taking an example as shown in Fig. 20. Let's consider that semiconductor-1 is MO-1 and semiconductor-2 and semiconductor-3 are MS-2 and MS-3. Firstly, percentage composition should be decided that out of 100 %, how much percentage of each layer could be used to develop the efficient nanocomposite based schemes. MO-1 layer can be 25 % because of wide band gap which can make the composite stable and only participate to transfer its charge carriers and MS-2 layer may be of 35 % due to smaller band gap and can absorb maximum visible light and maximum reduction reaction takes place from its CB. Meanwhile, the MS-3 layer may be 40 % with a small band gap which might be helpful to maintain stability, increase light absorption, enhance the charge transportation and take the holes from other two layers to increase the oxidation reaction at its VB (Fig. 20). Lastly, this scheme presented in Fig. 20 would be helpful to enhance the activity of nanocomposite by choosing different materials i.e.; metal-based or nonmetal-based semiconductors with adjustable percentage compositions and for different type of redox reactions depending upon the reduction and oxidation potentials of redox species to be utilized for their conversion as shown in Fig. 20.

Among all types of heterojunctions, the Z-scheme mechanism shows the best stability and excellent recyclability. The Z scheme heterojunction mechanisms are made by mimicking the process of natural photosynthesis. In this process, the photogenerated electrons of one semiconductor are recombined with holes of other semiconductor and highly energetic electrons and holes are eventually utilized for redox reactions. Simultaneously, the materials used in the Z scheme heterojunctions have robustness and resistance to photostability and enhance the long-term stability of the photocatalyst. Meanwhile, the S scheme heterojunction might still face issues related to degradation of materials over time. Therefore, Z scheme heterojunction material photocatalysts are preferred on the industrial scale due to their high photostability and recyclability for photocatalytic applications. In contrast, the photostability and recyclability of metal oxides and metal sulfide are also essential for photocatalytic application. The metal oxides such as TiO₂, ZnO and WO3 are well known for their excellent resistant to photo corrosion and maintain their structural catalytic behavior under light illumination. They also show stability under high pH levels and temperature. They retain their photocatalytic properties over multiple cycles due to their robust chemical nature and can also be recovered easily. Meanwhile, metal sulfides Bi₂S₃ and ZnS are prone to photo corrosion and degrade under continuous light illumination. They are not

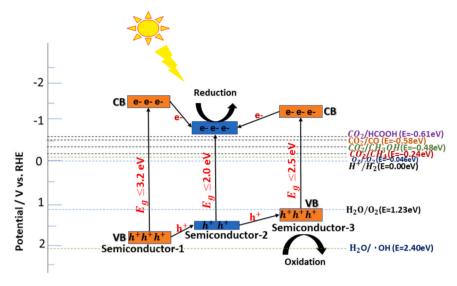


Fig. 20. Scheme for semiconductors with different band alignments for transportation of charge carriers.

chemically stable and react in the presence of oxygen and water. For industrial and environmental application metal oxides are preferred due to their better stability and recyclability for photocatalytic application.

5. Role of nano pyrophosphate in the catalyst for photocatalytic reactions

Nano pyrophosphates are basically nanoparticles composed of pyrophosphates having two phosphorus atoms and seven oxygen atoms. They play a significant role in catalysis due to their unique characteristics. i) They have high surface area and provide large number of active sites for catalytic reactions, ii) They have specific band gap energies which is comparable with the energy of solar light which generate electron-hole pairs, increase charge separation and reduce charge recombination, iii) The surface can be modified with various metals and metal oxides and improve the adsorption of reactants for better light absorption and charge transfer and iv) They are chemically and thermally stable and facilitate better photocatalytic reactions without degradation in the high temperature.

To get deep insight into the role of nano pyrophosphates different examples containing metal nano pyrophosphates would be discussed. Nickel pyrophosphate possesses good conductivity, large storage sites, broad channels for electrolyte ions movement, stable structure due to P-O bond. It is synthesized by co-precipitation method and used for degradation of methylene blue. 300-C calcined Nickel pyrophosphate nanoparticles were used for decolorization and degradation of 10ppm MB dye in the presence of UV and solar light. In the UV light source and 90 minutes stirring the mineralization efficiency reaches 83.1 %. Meanwhile, in the solar light MB dye solution exhibited 95.06 % photodegradation [156]. The photocatalytic mechanism of Nickel pyrophosphate nanoparticles is shown in Fig. 21. Similarly, Defect rich cobalt pyrophosphate modified with Cd_{0.5}Zn_{0.5}S was synthesized for photocatalytic hydrogen generation. Cobalt-phosphonate-derived cobalt pyrophosphate hybrids (CoPPi-A) is a novel and hydrophilic cocatalyst with Cd_{0.5}Zn_{0.5}S photocatalyst having controlled pH and optimized interface was used to produce 6.87mmolg⁻¹h⁻¹ photocatalytic hydrogen [157]. The nano pyrophosphates nanoparticles are advanced materials in the field of photocatalysis. They are widely used for water splitting and dye degradation from few days ago but their applications are very limited for CO₂ reduction and H₂O₂ production. The further development for the utilization of different kinds of nano pyrophosphates are required in the field of photocatalysis and energy

Table 3Metal Sulfide-Metal Sulfide based composites for photocatalytic applications:.

| Photocatalysts- Sensitizers | Synthesis Methods | Heterojunctions | Activity | References |
|--|--|--------------------------|--|------------|
| MnIn ₂ S ₄ -Cu ₇ S ₄ | Oil bath stirring-Hydrothermal | Type-II | Photocatalytic production of H ₂ is 13.81 μmol/g/h | [140] |
| CdS-Bi ₂ S ₃ | Sono chemical-Sono chemical | Type-II | Photocatalytic production of H ₂ is 5500 µmol/g/h | [141] |
| CdS-ZnS | AACVD-AACVD | Type-II | Photocurrent density is 8.02 mA/cm ² vs. NHE | [142] |
| In_2S_3 -Cd In_2S_4 | Cation exchange reaction-hydrothermal | Type-II | Photocatalytic production of CO is 825 $\mu mol\ h^{-1}\ g^{-1}$ from CO_2 reduction | [144] |
| CdS-ZnIn ₂ S ₄ | Water bath heating-Solvothermal | Direct Z-scheme | Photocatalytic production of H ₂ is 540.3 μmol/g/h | [145] |
| Bi ₂ S ₃ -SnIn ₄ S ₈ | Solvothermal-Solvothermal | Direct Z-scheme | Photodegradation of Rh B is 99.87 % | [146] |
| MoSe ₂ -Bi ₂ S ₃ -CdS | Solvothermal-Hydrothermal- Hydrothermal | Dual Direct Z- scheme | Photocatalytic production of H_2 is 11840 μ mol/g/h | [147] |
| CdS-MoS ₂ QDs-ZIS | Solvothermal-Solvothermal- Hydrothermal | Solid-state Z-scheme | $\rm H_2$ production is 2107.5 μ mol/g/h | [148] |
| ZnS-rGO-Bi ₂ S ₃ | Hydrothermal-Hydrothermal- Hydrothermal | Solid-state Z-scheme | $\rm H_2$ production is 2523.4 $\mu mol/g/h$ and photocurrent density are 38 $\rm mA/\it cm^2$ | [149] |
| Cd/CdS-Co ₉ S ₈ | Hydrothermal-Sacrificial Template method | Solid-state Z-scheme | $\rm H_2$ production is 10.42 μ mol/h | [150] |
| CdS-FeS ₂ | Hydrothermal-Hydrothermal | S-scheme | Photocatalytic production of H ₂ is 107.56 μmol/g/h | [151] |
| ZIS-FeS ₂ | Water-bath Hydrothermal | S-scheme | Photocatalytic production of H ₂ is 10100 µmol/g/h | [152] |
| ZnS-ZIS | Hydrothermal-hydrothermal | S-scheme | H ₂ production is 2912.3 μmol/g/h | [153] |
| CuS-ZIS | Hydrothermal-Hydrothermal | S-scheme | H ₂ production is 4653.43 μmol/g/h | [154] |
| Bi ₂ S ₃ /CdS | Hydrothermal | S-scheme | H_2O_2 production 212.82 µmol L ⁻¹ | [155] |

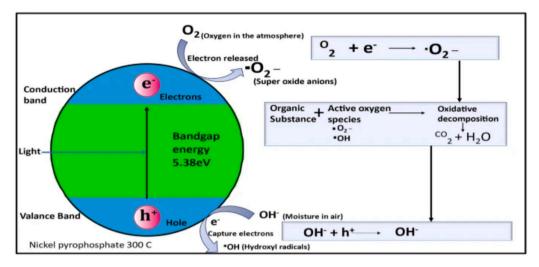


Fig. 21. Photocatalytic mechanism of Ni2P2O nanoparticles. Reproduced with permission [156]. Copyright 2024, Journal Material Sciences.

storage applications.

6. Conclusion and future perspectives

In the last few years, many investigations have been reported on constructing heterojunctions in binary and ternary composites of metal oxides and metal sulfides for photocatalysis. In this review article, the incisive appraisal on recent achievements in the area of heterojunction to improve water splitting, CO2 reduction, photodegradation of dyes and H₂O₂ production by low-cost metal oxides and metal sulfides is presented. To create heterojunction between the photocatalysts systematic strategies are discussed. The strategies include band position alignment for charge transfer, formation of interface to produce internal electric field, charge separation and recombination of useless charge carriers and finally reduction of protons to produce hydrogen, reduction of ${\rm CO_2}$ to produce alcohols, formic acid, CO and oxidation of dyes. It is further improved by surface modification like; by producing surface plasmon resonance effect and conductive bridges in between the photocatalysts. Further directions in this area should be focused on these aspects: i) More advancement in the morphology, interface formation and crystal structure to improve the stability of metal sulfides and to reduce the band gap of metal oxides are needed, ii) Utilization of noble metals and transition metal as SPR and conductive bridge for charge transfer and production of internal electric field in binary, ternary and quaternary heterojunctions should be studied further to improve the activities of photocatalysts commercially, iii) To design multicomponent photocatalysts proper understanding of interactions between layers, positive response to visible light, shortening of band gap and stability after heterojunction should be upgraded and iv) Cost effective and optimal metal oxide and metal sulfide cocatalysts and catalysts should be used as protective layer to make the environment pollution free.

After getting deeper insight into all type of heterojunctions there are few future development technology for formation of heterojunctions are needed: (i) Explore heterojunctions with ternary and quaternary semiconductors for optimization of band alignment, enhancing the light absorption spectrum and charge carrier dynamics (ii) Development of specific techniques to control heterojunction interface, improve charge carrier kinetics and long-term stability (iii) Advanced nanofabrication techniques are required to create heterojunctions with controlled dimension and high surface area to facilitate rapid charge transfer (iv) In situ and operando characterization methods are required to study the heterojunction dynamics with realistic operating conditions such as computational simulation and modeling for proper band alignment and charge transfer mechanisms (v) Foster collaboration between academia and industry is needed to harness the heterojunction potential for

addressing global challenges and creating new opportunities in energy applications and environmental sustainability.

CRediT authorship contribution statement

Alisha Shabbir: Writing – original draft, Formal analysis, Data curation, Investigation, Methodology. Asad Mumtaz: Writing – review & editing, Visualization, Validation, Supervision, Software, Resources, Project administration, Methodology, Investigation, Conceptualization, Writing – original draft. Sabahat Sardar: Writing – review & editing, Validation, Data curation, Writing – original draft.

Declaration of Competing Interest

The authors declare that they have no known competing financial interests or personal relationships that could have appeared to influence the work reported in this paper.

Data Availability

Data will be made available on request.

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Interest statement

Authors declare no competing financial interests.

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